

*ALS User's Meeting, Berkeley, CA*  
*October 2000*

# ***Ultrafast X-ray Diffraction in Solids using K Radiation from Femtosecond Laser Generated Plasma Sources***

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Universität Essen, Germany***

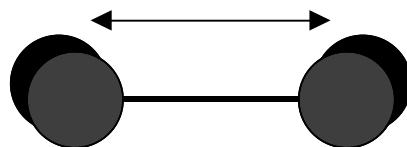
# *Why ultrafast x-rays ?*

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***Directly observe ultrafast atomic motion***

1 Å or ~10 keV



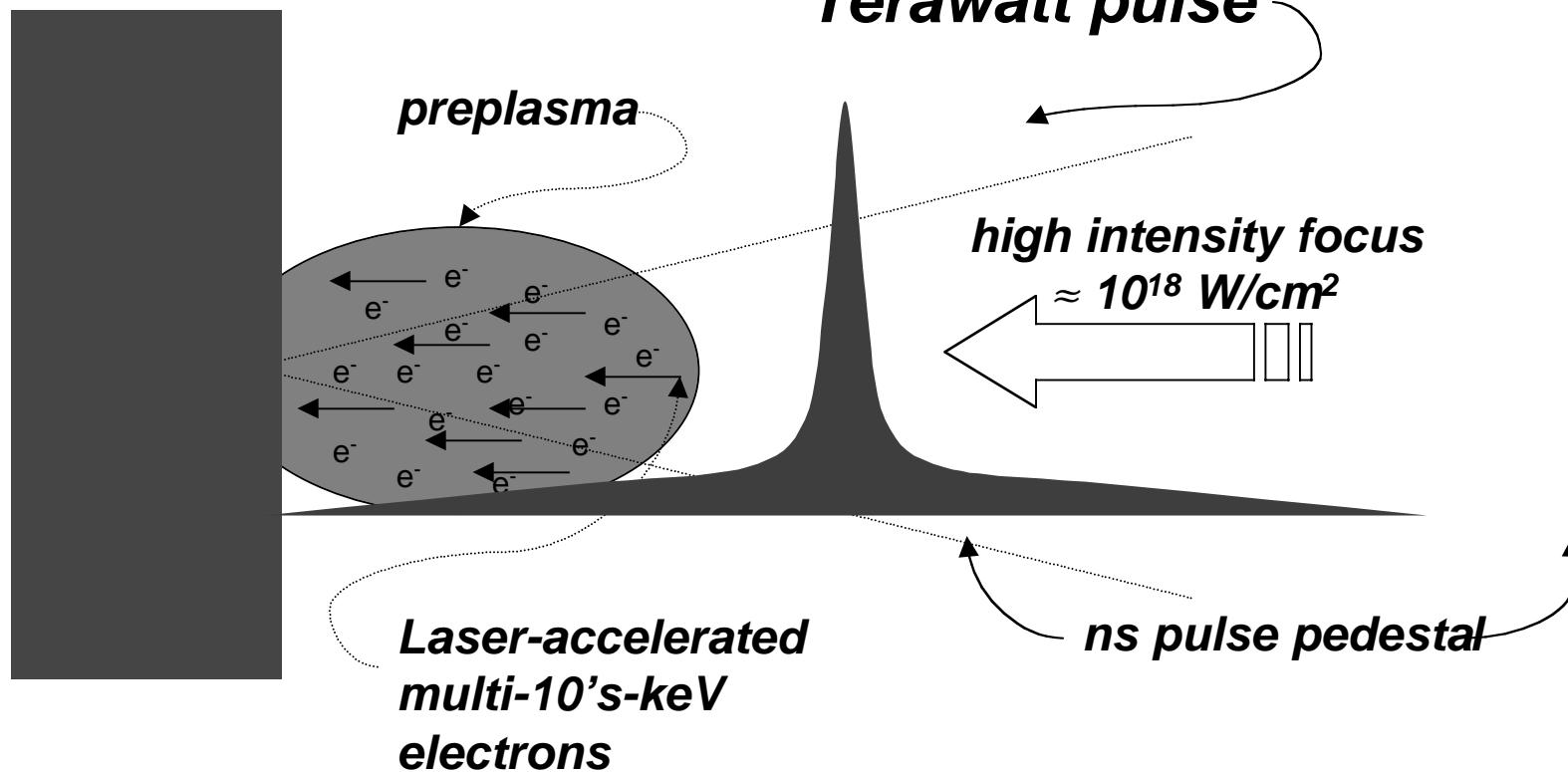
**1) Short pulses (fs to ps)**

**2) Hard x-ray radiation**

# Laser-driven Electrons for Fast X-rays



*solid target*

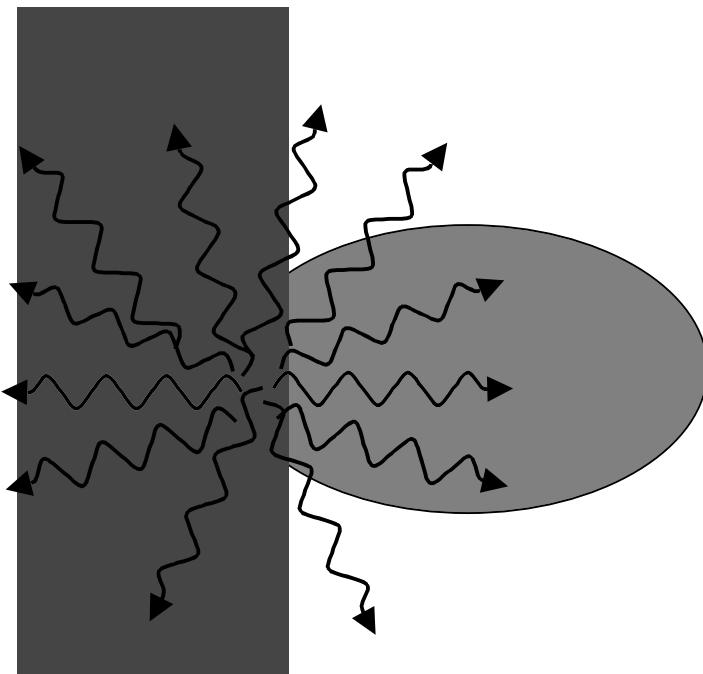


J.D. Kmetec, et al., *Phys. Rev. Lett.* **68**, 1527 (1990).

# Laser-driven Electrons for Fast X-rays



***solid target***

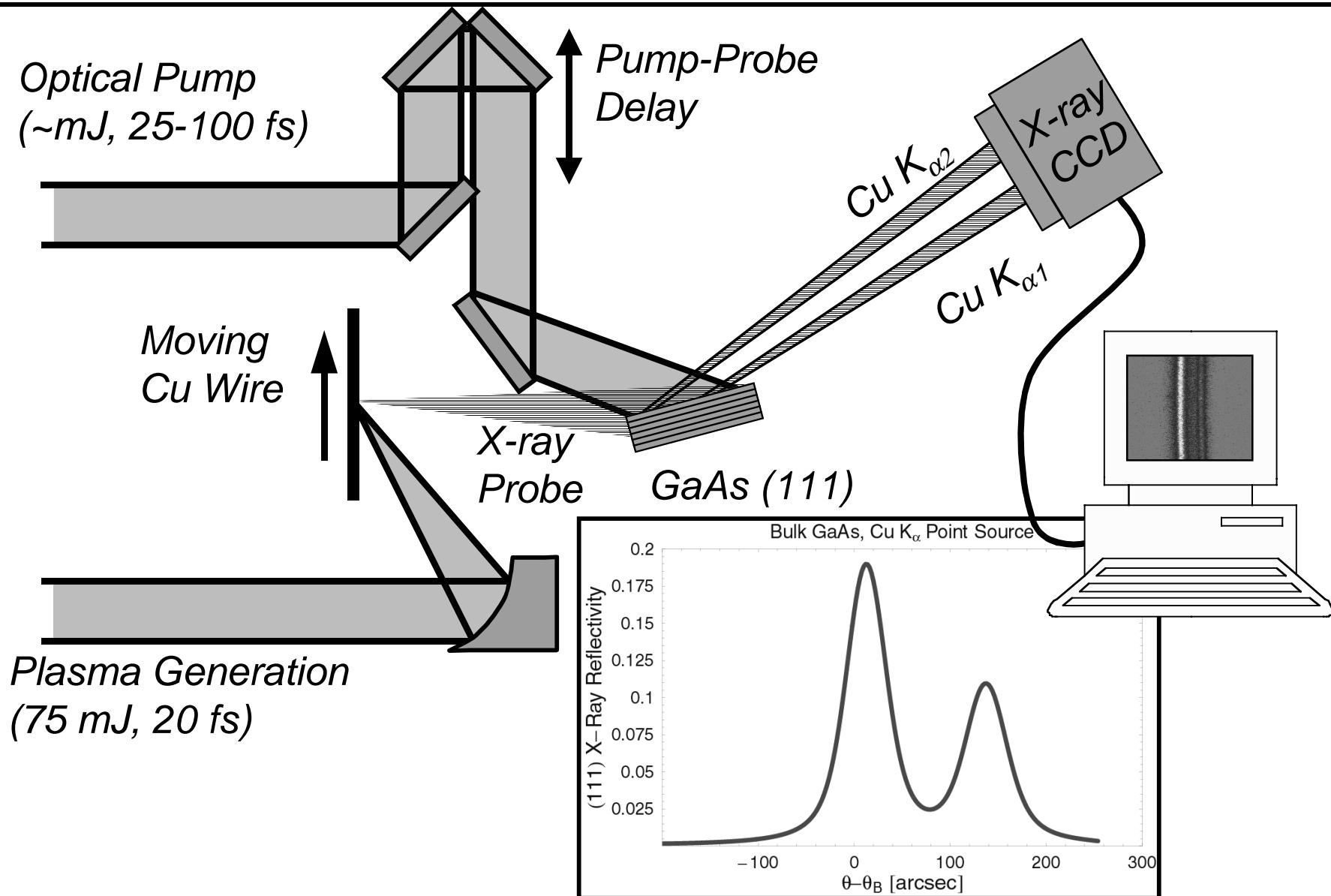


- **x-ray pulse duration:**  
 $\Delta t_{\text{electron}}$  and stopping  
time
- ~ 200 fs at ENSTA
- Source size ~ laser spot
- $10^9$  photons / shot

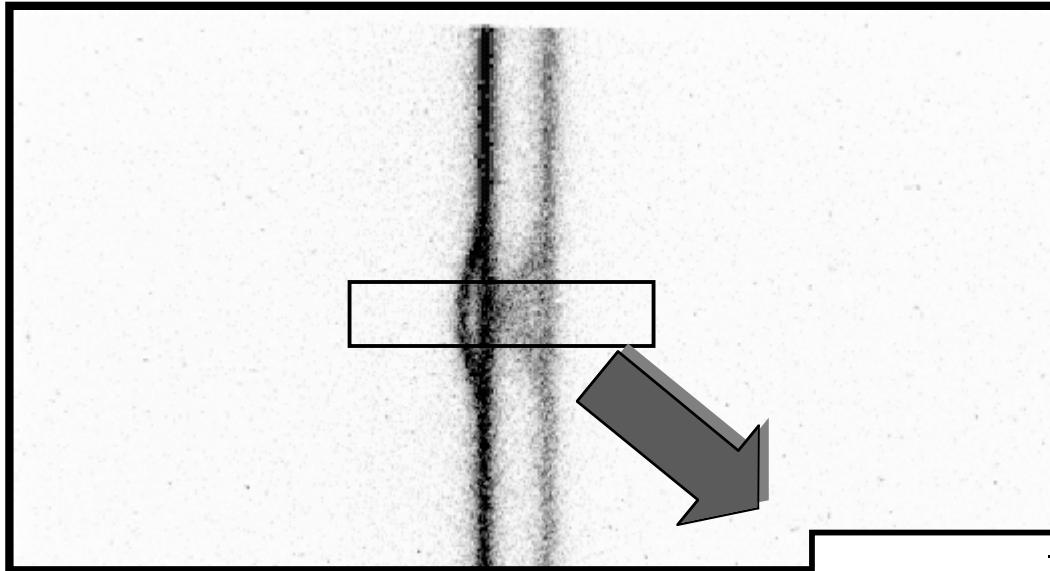
**Bremsstrahlung and  $K_\alpha$  radiation**

J.D. Kmetec, et al., *Phys. Rev. Lett.* **68**, 1527 (1990).

# Ultrafast X-ray Diffraction



Vertical Position



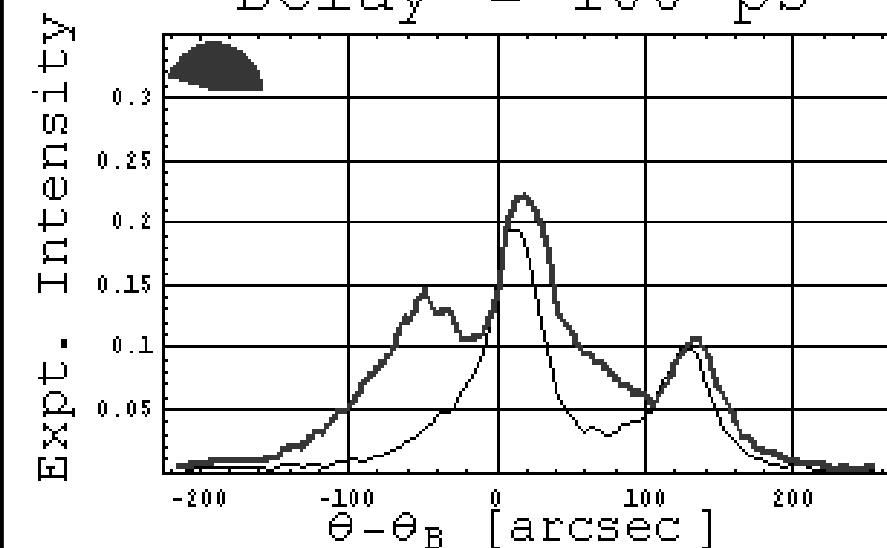
Diffraction Angle

$F = 50 \text{ mJ / cm}^2$

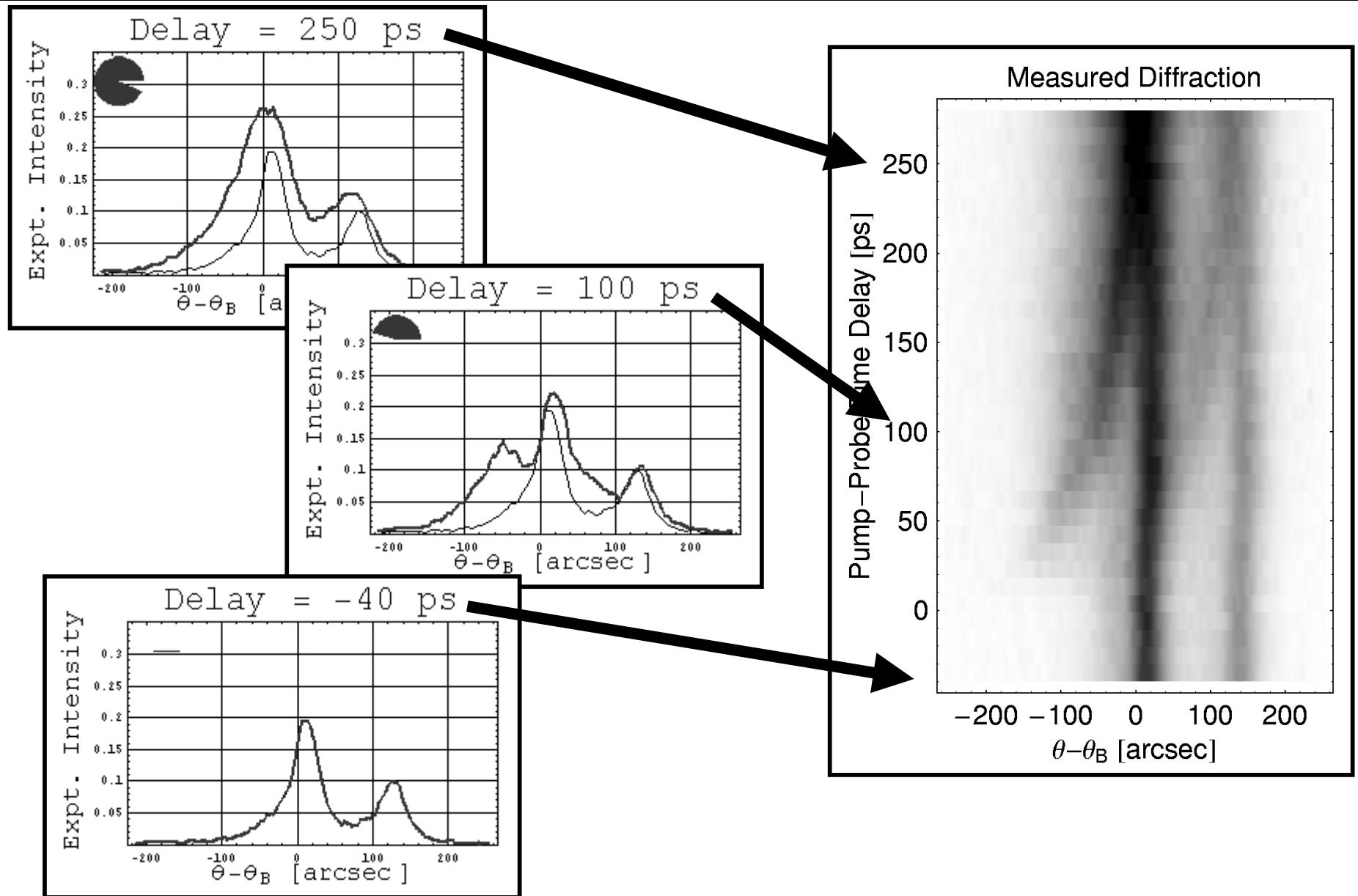
$\tau = 30 \text{ fs}$

***Integrated  
Lineouts***

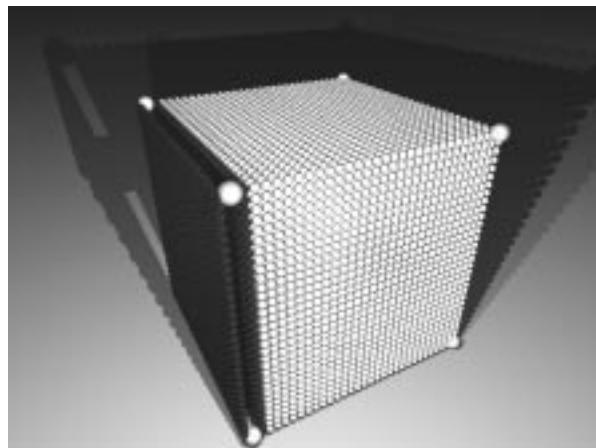
Delay = 100 ps



# Ultrafast X-ray Diffraction: GaAs

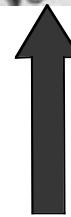
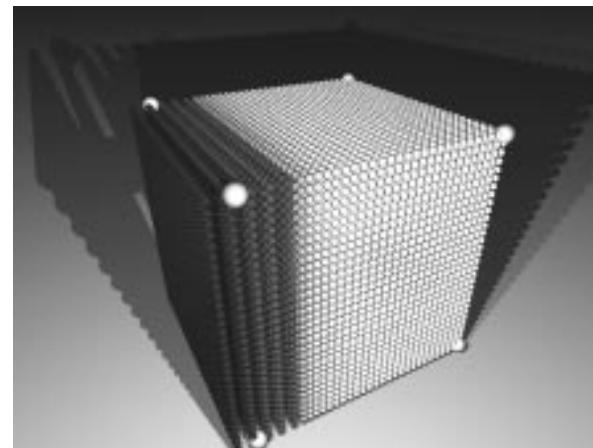


# Coherent Acoustic Phonons



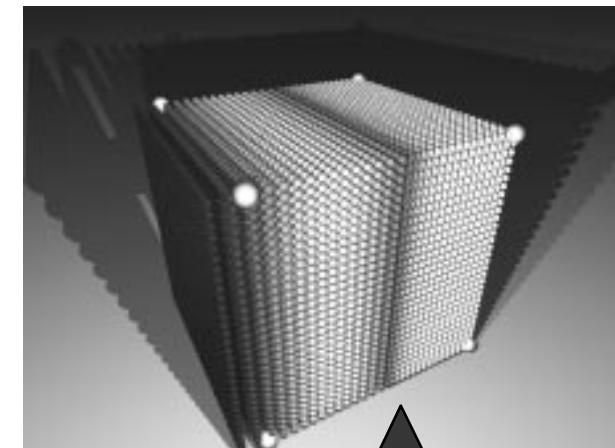
*Fast heating at  
constant Volume*

**Stress**



*Surface expansion*

**Strain**

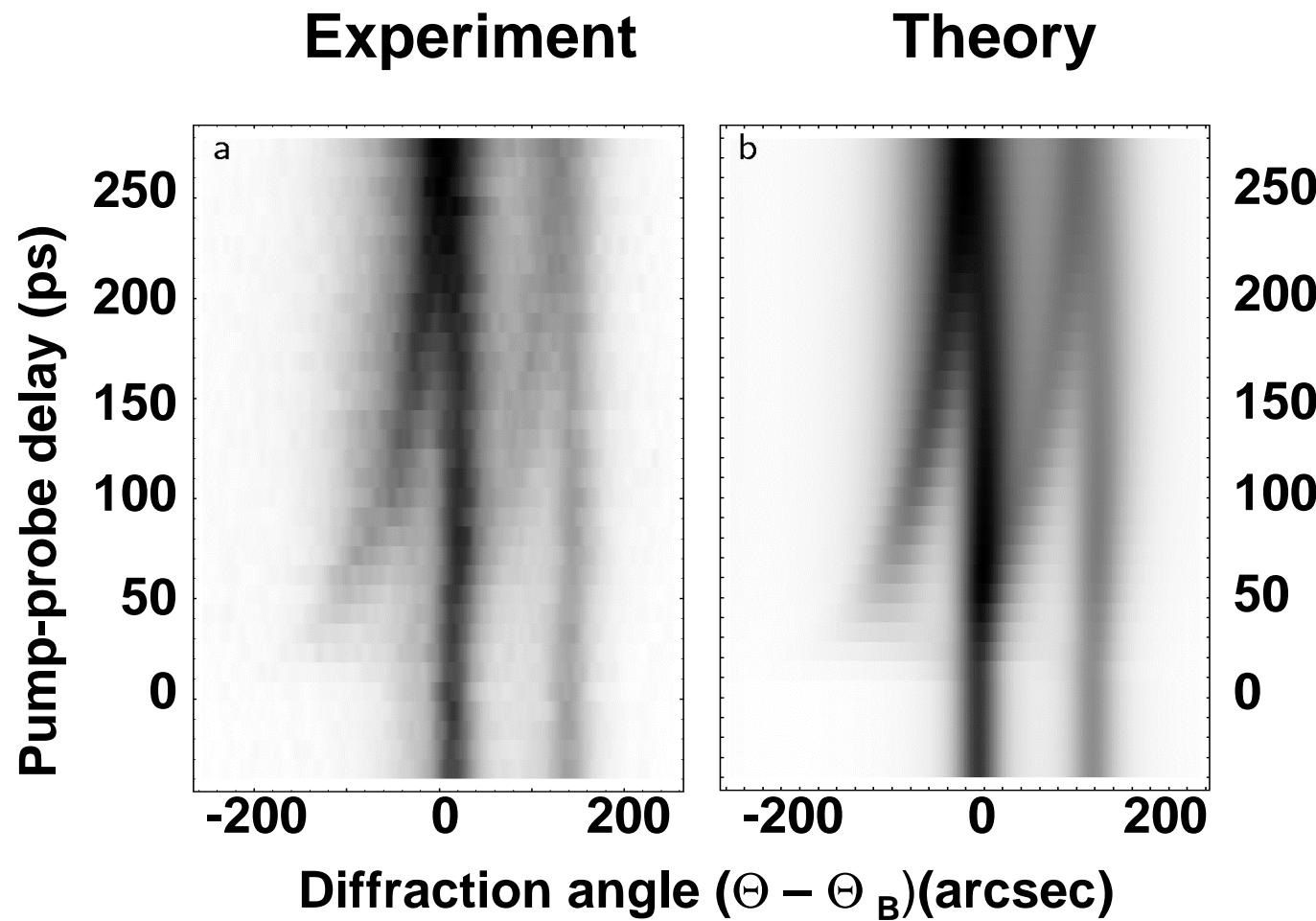


*Newton's 3<sup>rd</sup> Law*

**Acoustic  
Pulse**

C. Thomsen et al. Phys Rev. B 34, 4129 (1986).

# Gallium Arsenide



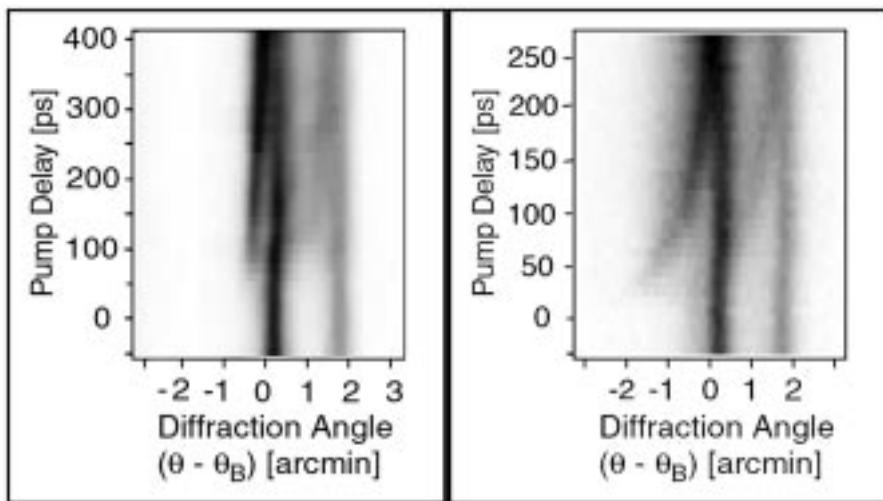
Ch. Rose-Petruck et al. *Nature* 398, 310 (1999).

# Heating depths



## Experiment

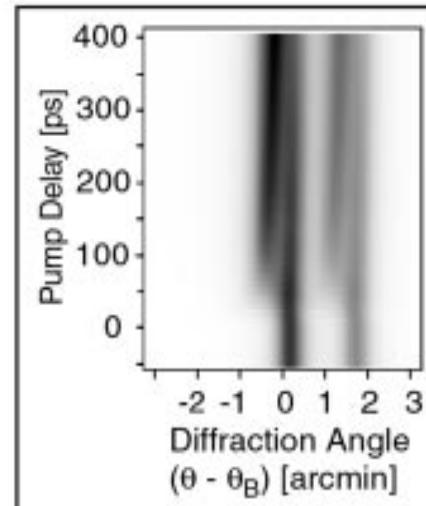
**Ge**



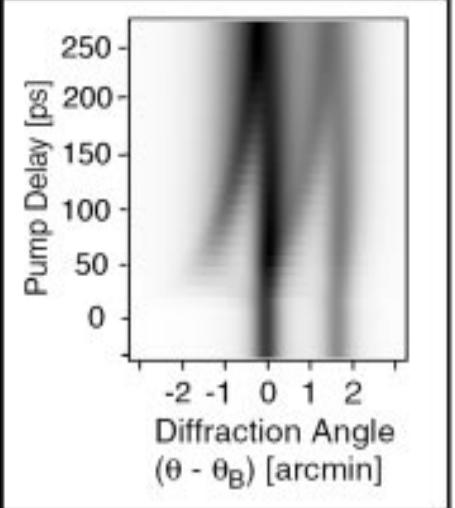
**GaAs**

## Theory

**Ge**



**GaAs**



$$\zeta = 1 \mu m$$

$$\zeta = 275 \mu m$$

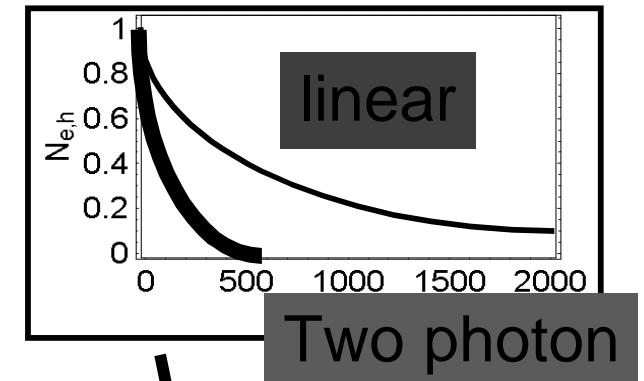
# Heating depths



## Two-temperature model

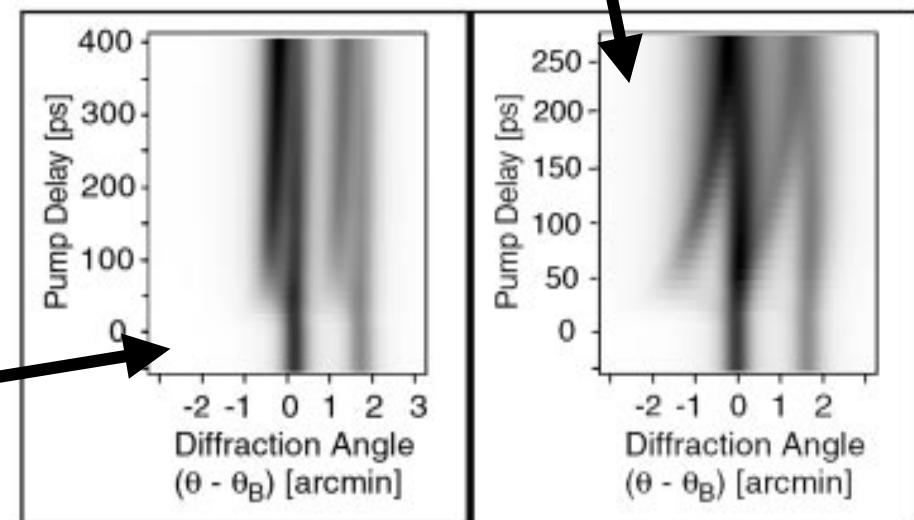
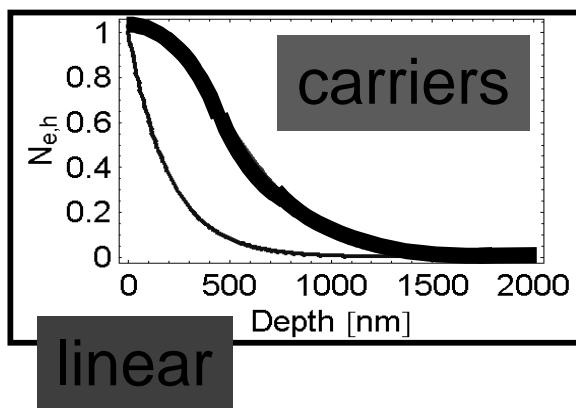
- ✓ Two photon absorption
- ✓ High density carrier diffusion
- ✓ Auger recombination coefficients

GaAs

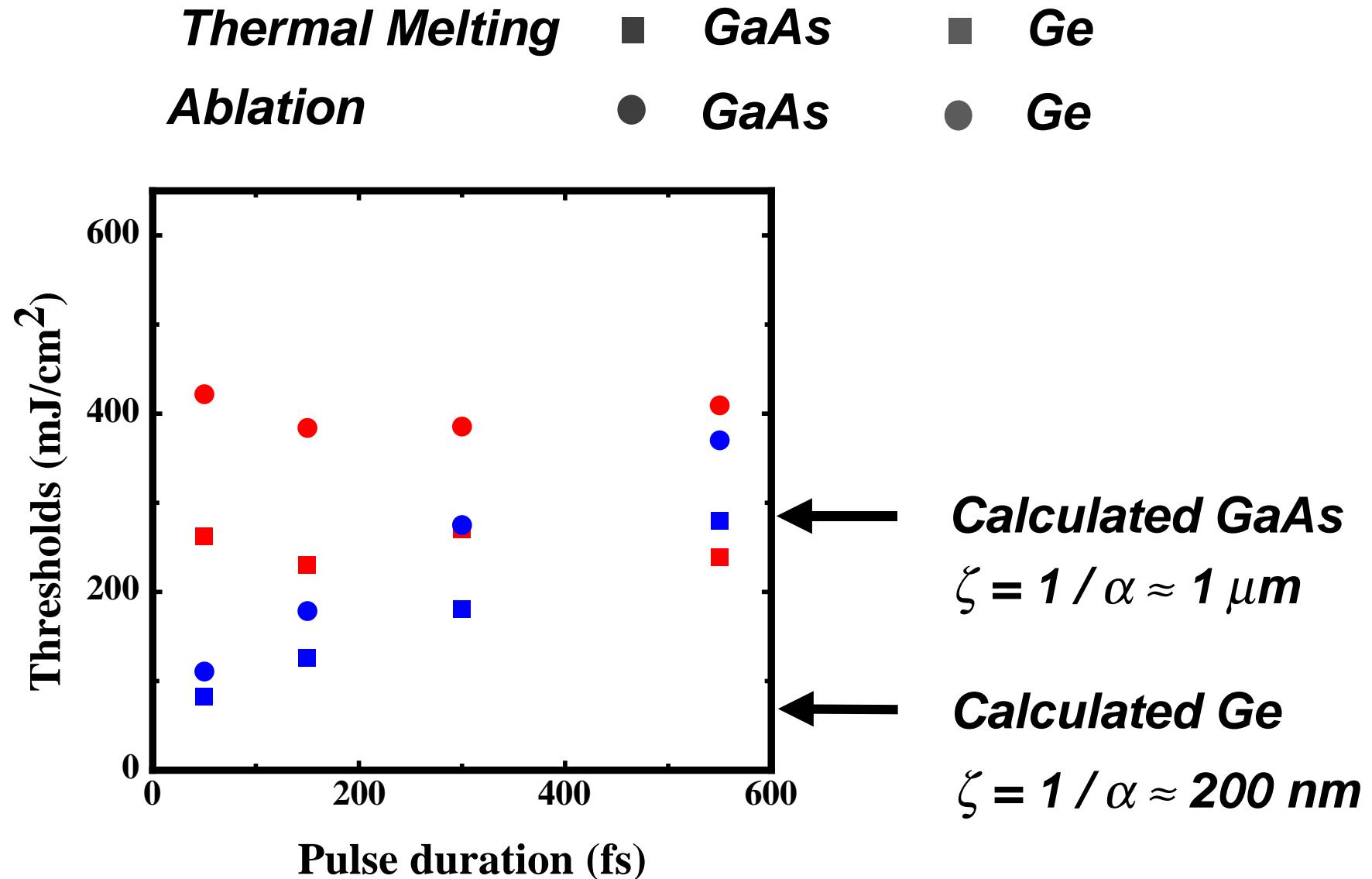


Two photon

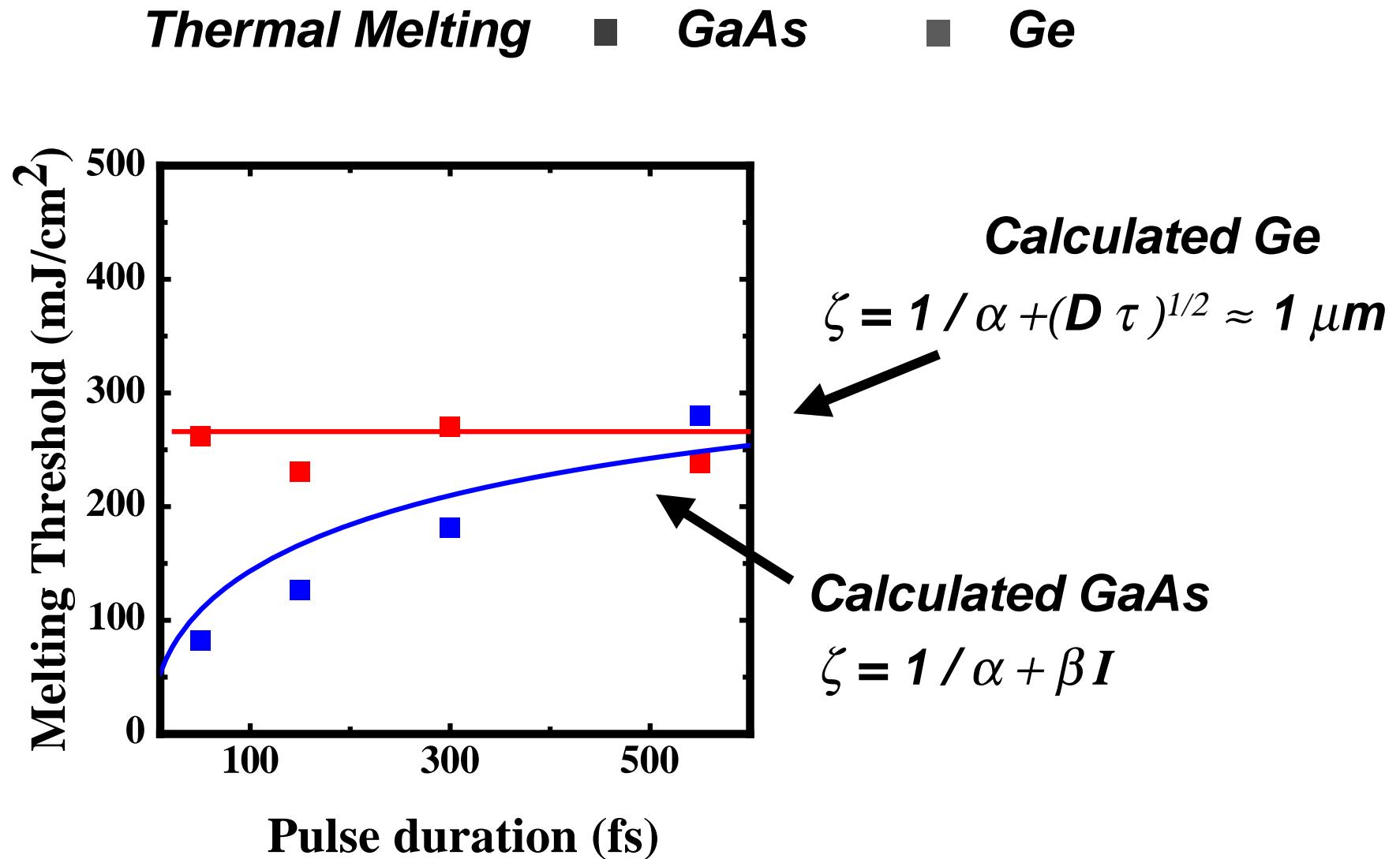
Ge



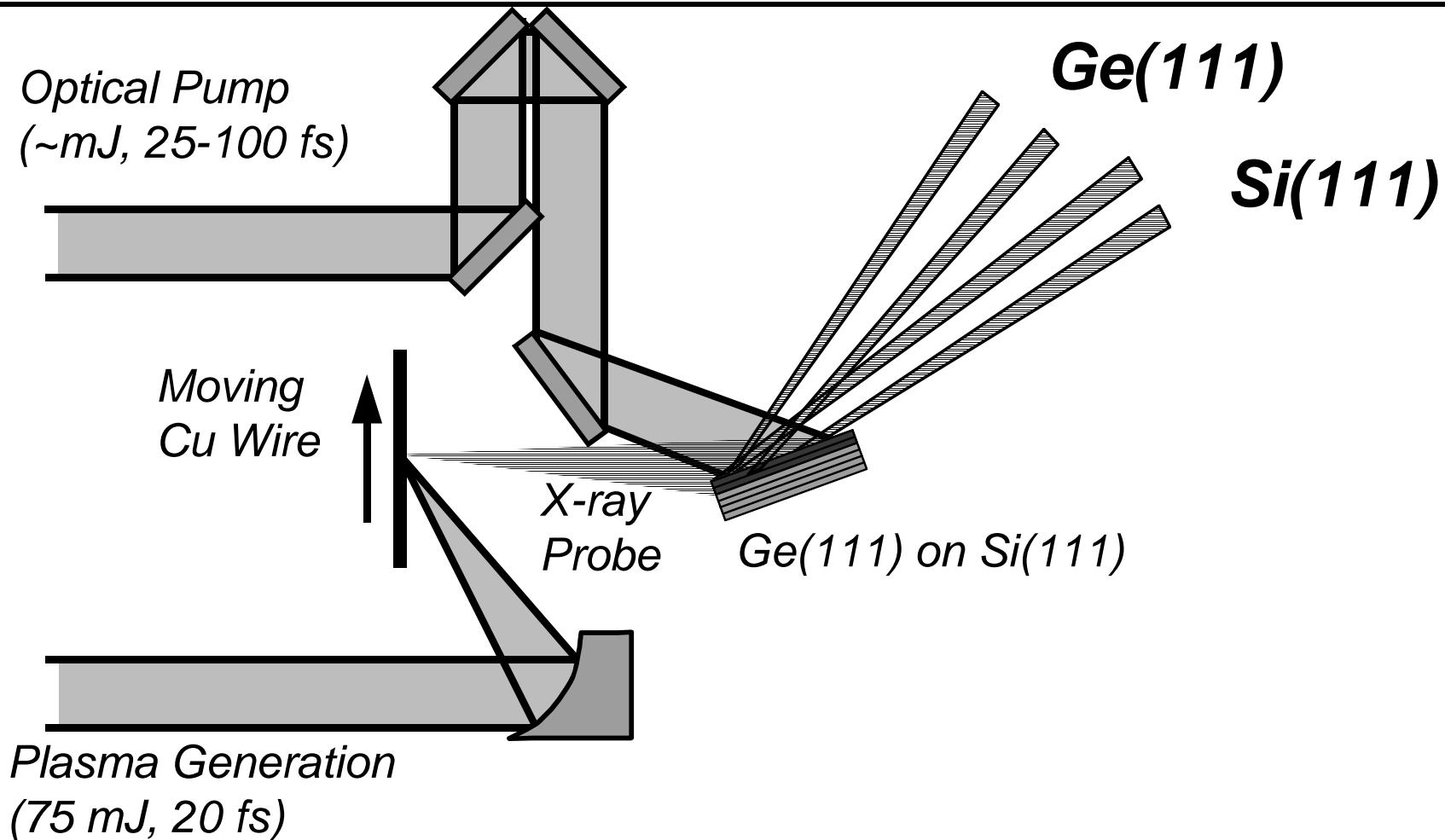
# Dependence on pulse duration



# Dependence on pulse duration



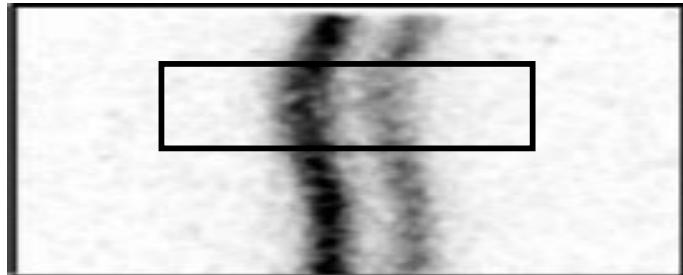
# Probing Hetero-structures



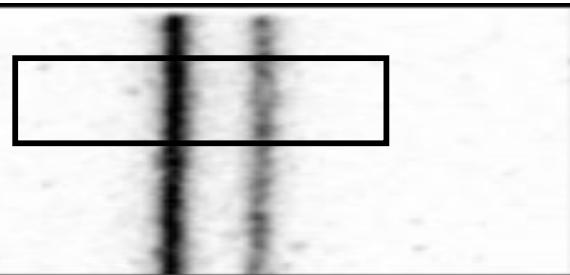
# *Centroid positions (400 nm film)*



**Ge**

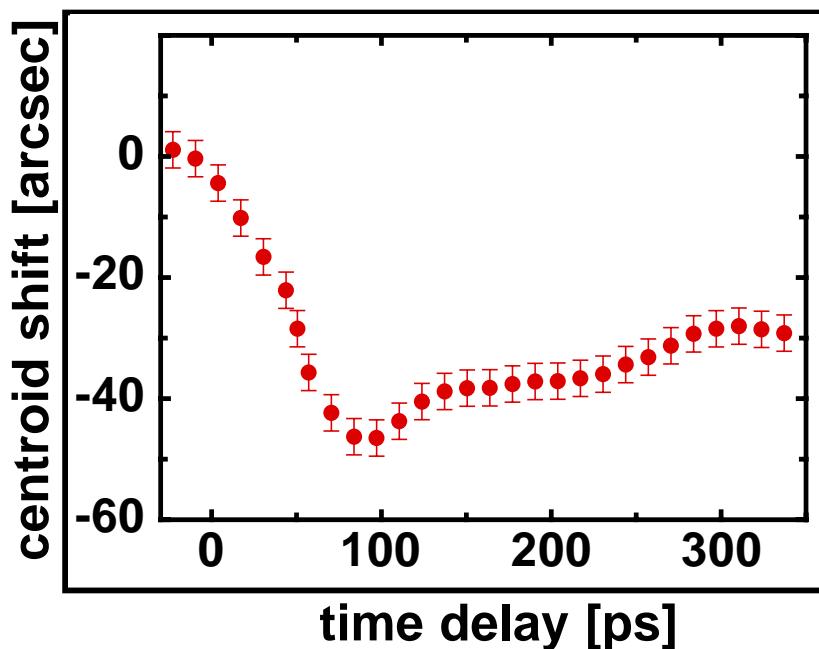


**Si**

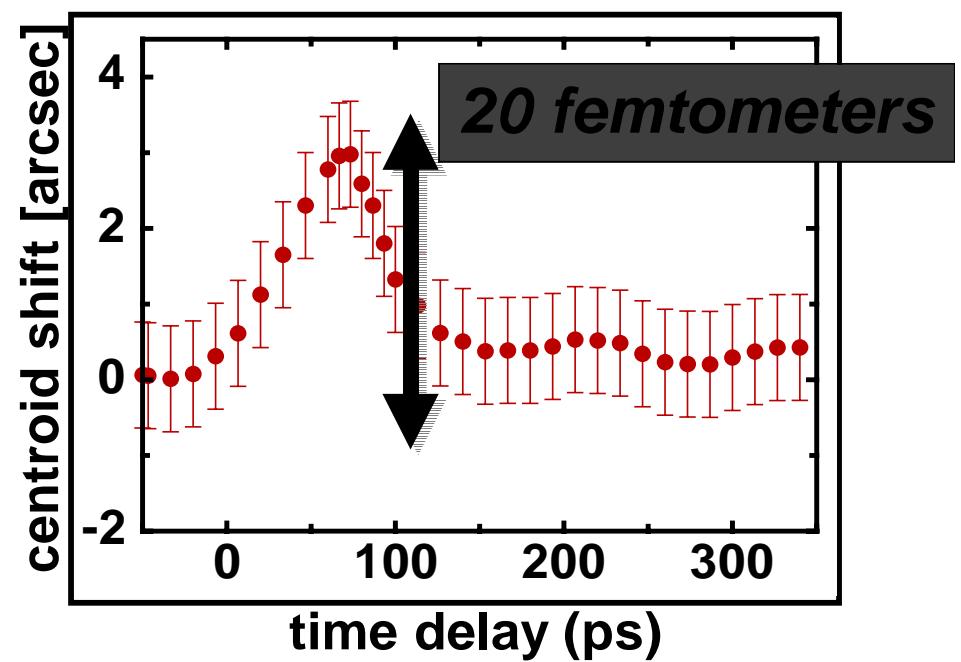


$$\tau_{\text{delay}} = 100 \text{ ps}$$

**Expansion**

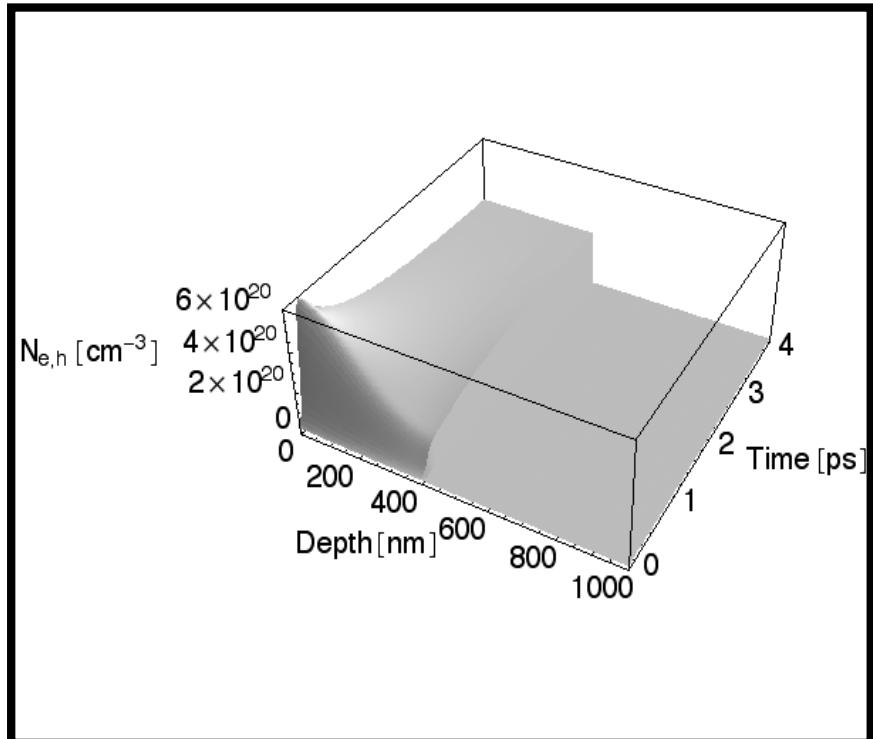


**Compression**

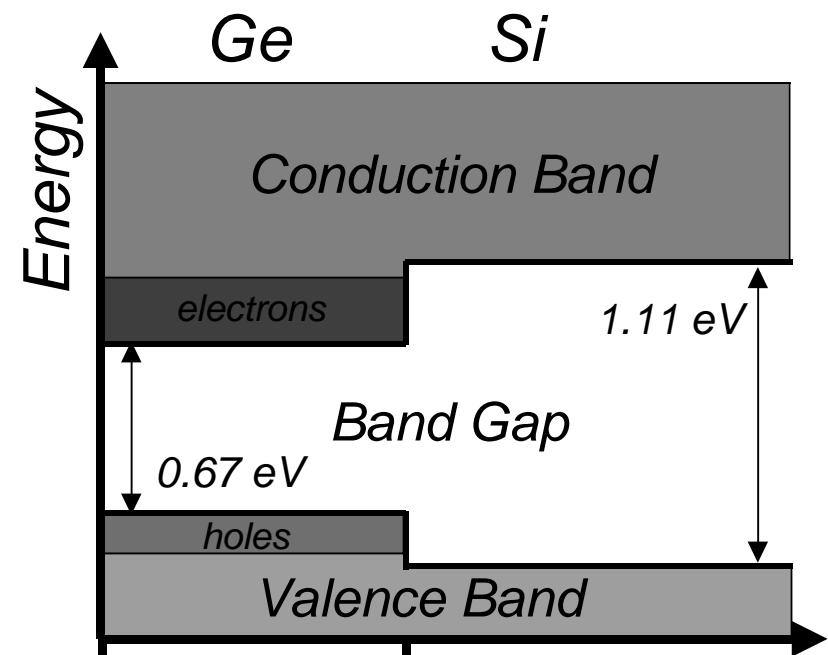


**20 femtometers**

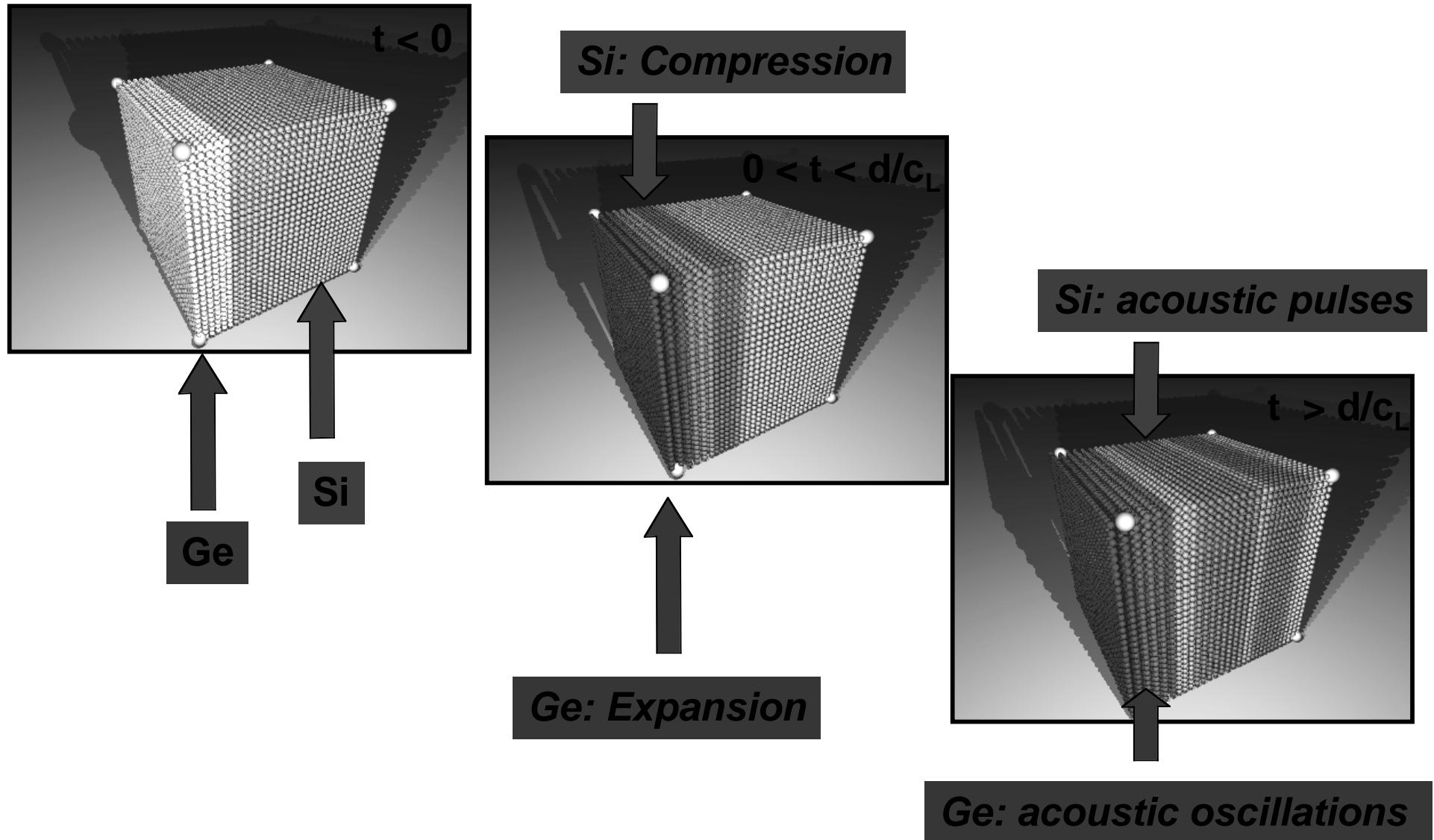
# Carrier dynamics (400 nm)



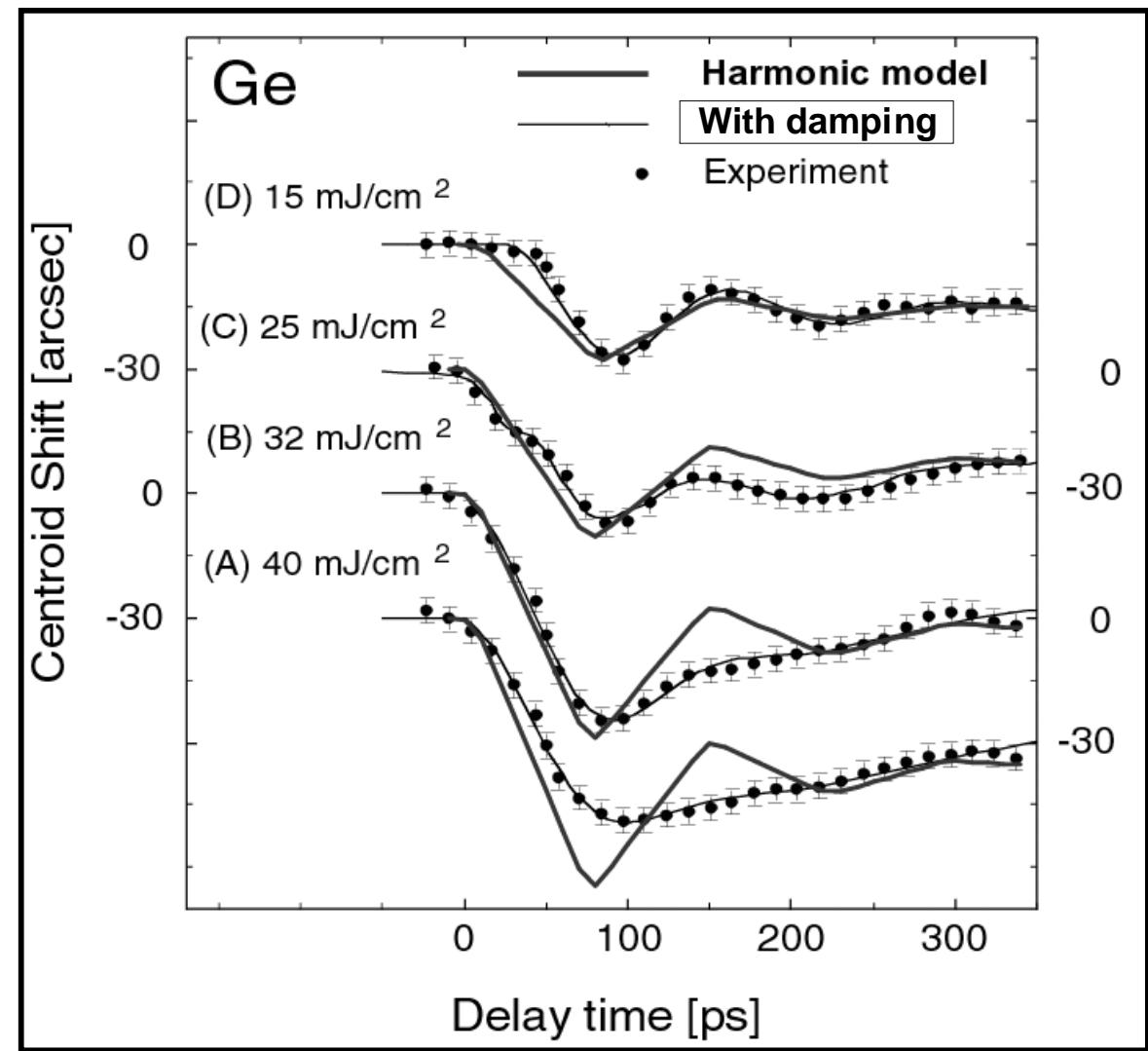
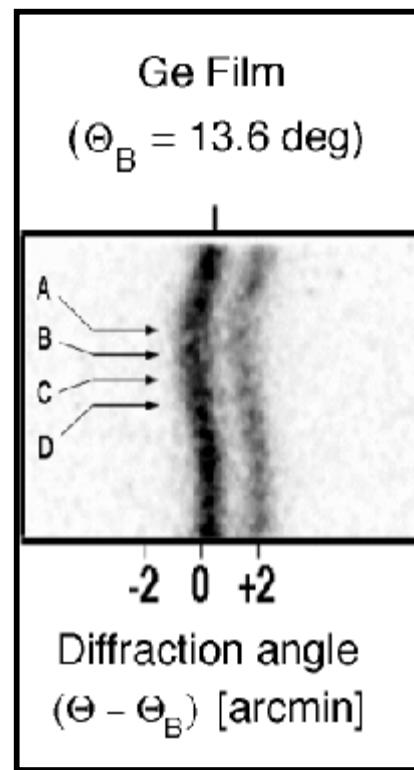
- ✓ Only Ge absorbs
- ✓ Carrier diffusion
- ✓ Carriers are confined



# Coherent Acoustic Phonons: Films



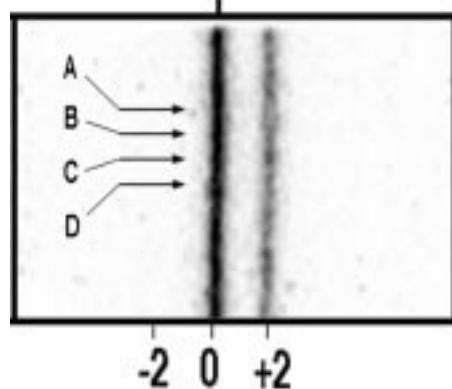
# Fluence Dependent Damping



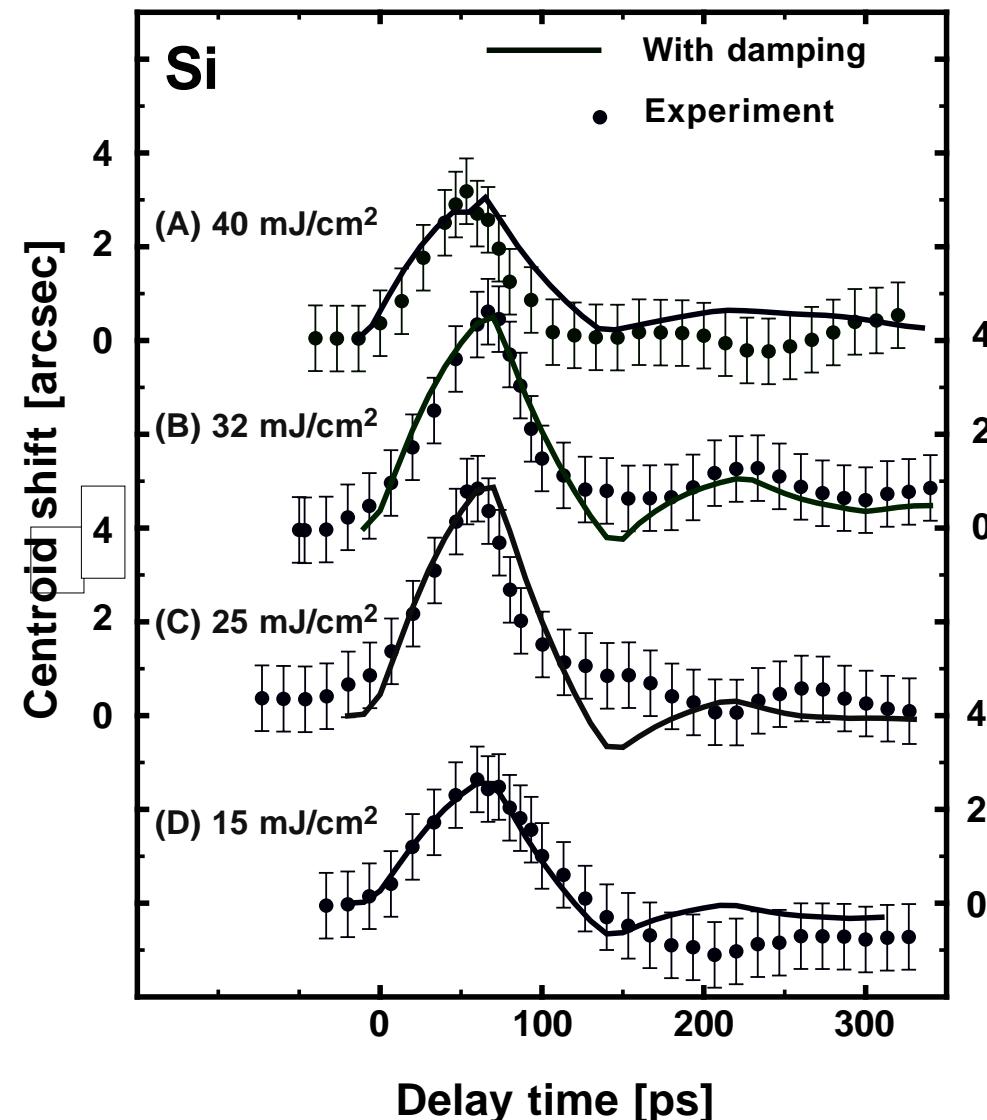
# Fluence Dependent Damping



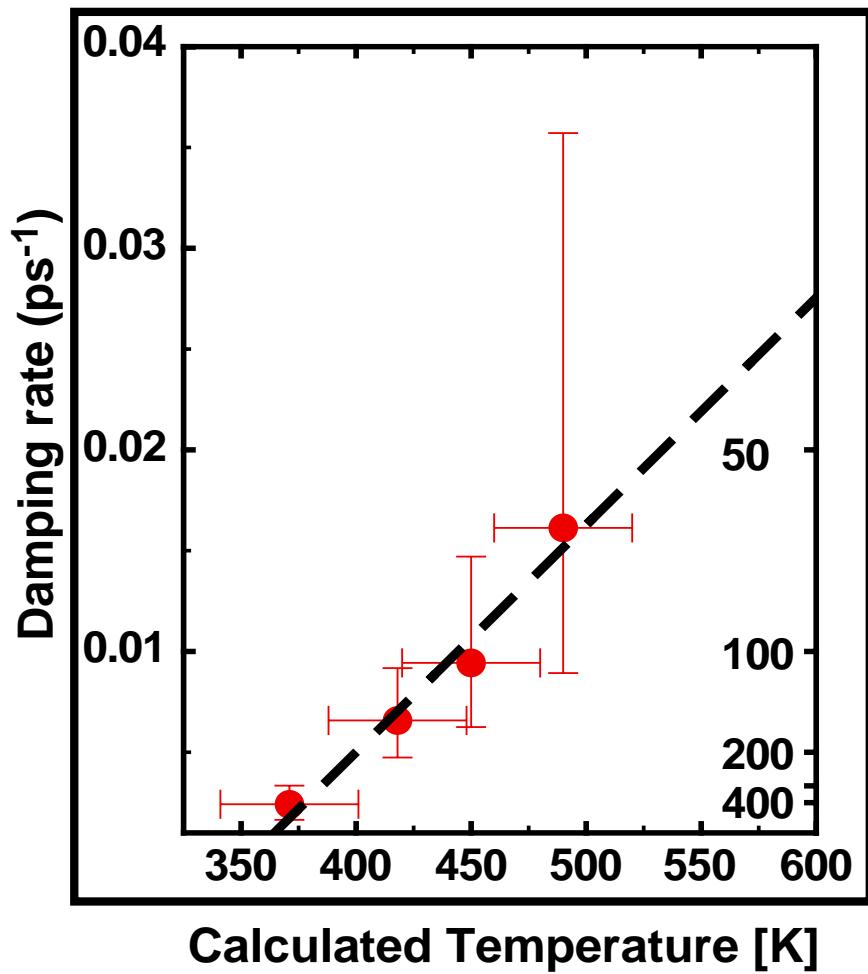
Si Substrate  
 $(\Theta_B = 14.2 \text{ deg})$



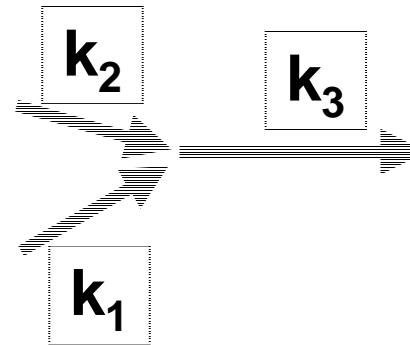
Diffraction angle  
 $(\Theta - \Theta_B)$  [arcmin]



# Coherent Phonon Damping Times

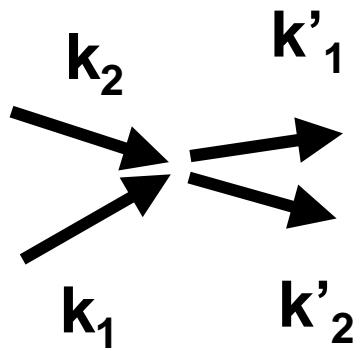


## Phonon collision



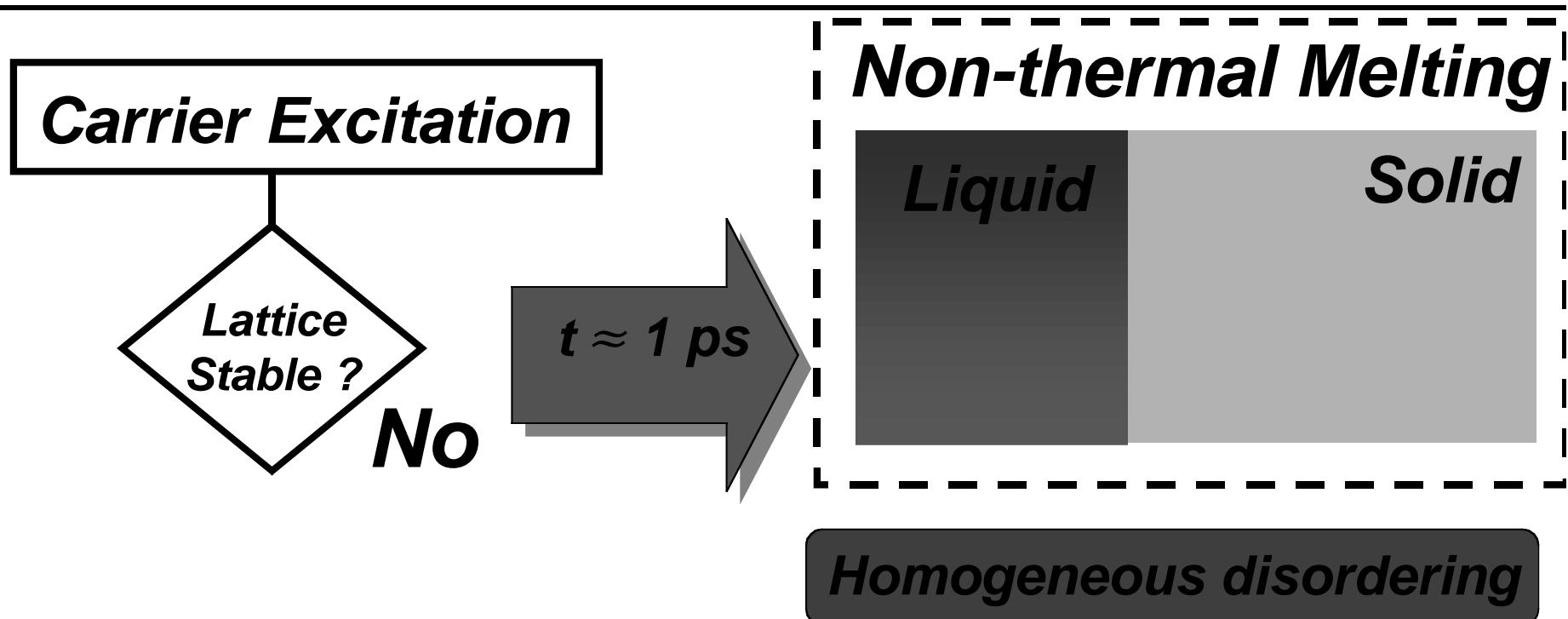
Damping time (ps)

## Phonon dephasing



A. Cavalleri et al., *Phys. Rev. Lett.* 85, 586 (2000)

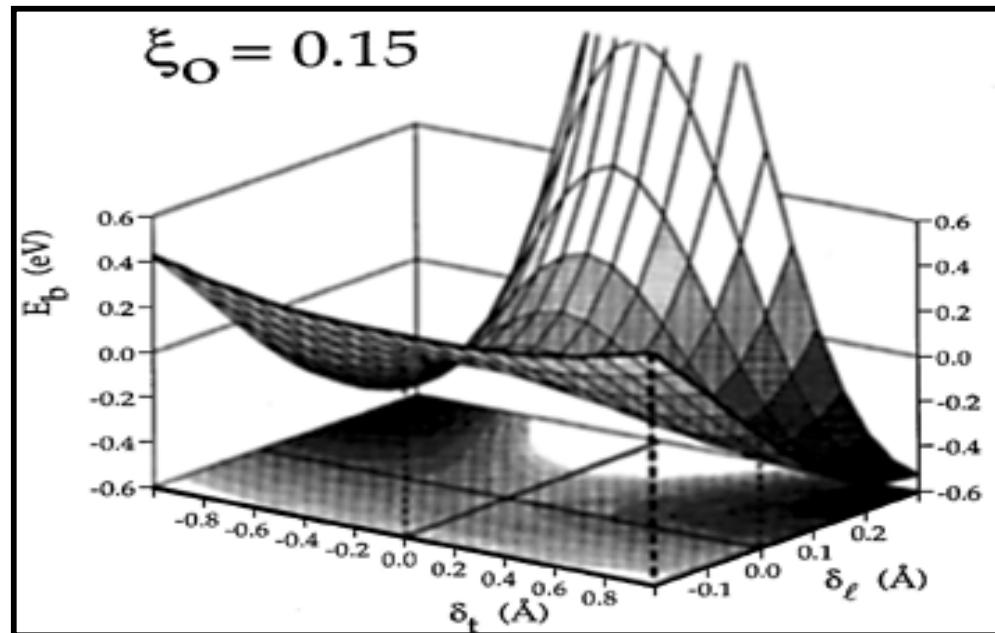
# *Ultrafast Melting Dynamics*



J.A. van Vechten et al., *Phys. Lett. A* 74A, 422 (1979).

P.L. Silvestrelli et al., *Phys. Rev. Lett.* 77, 3149 (1996).

## Potential Energy Surface

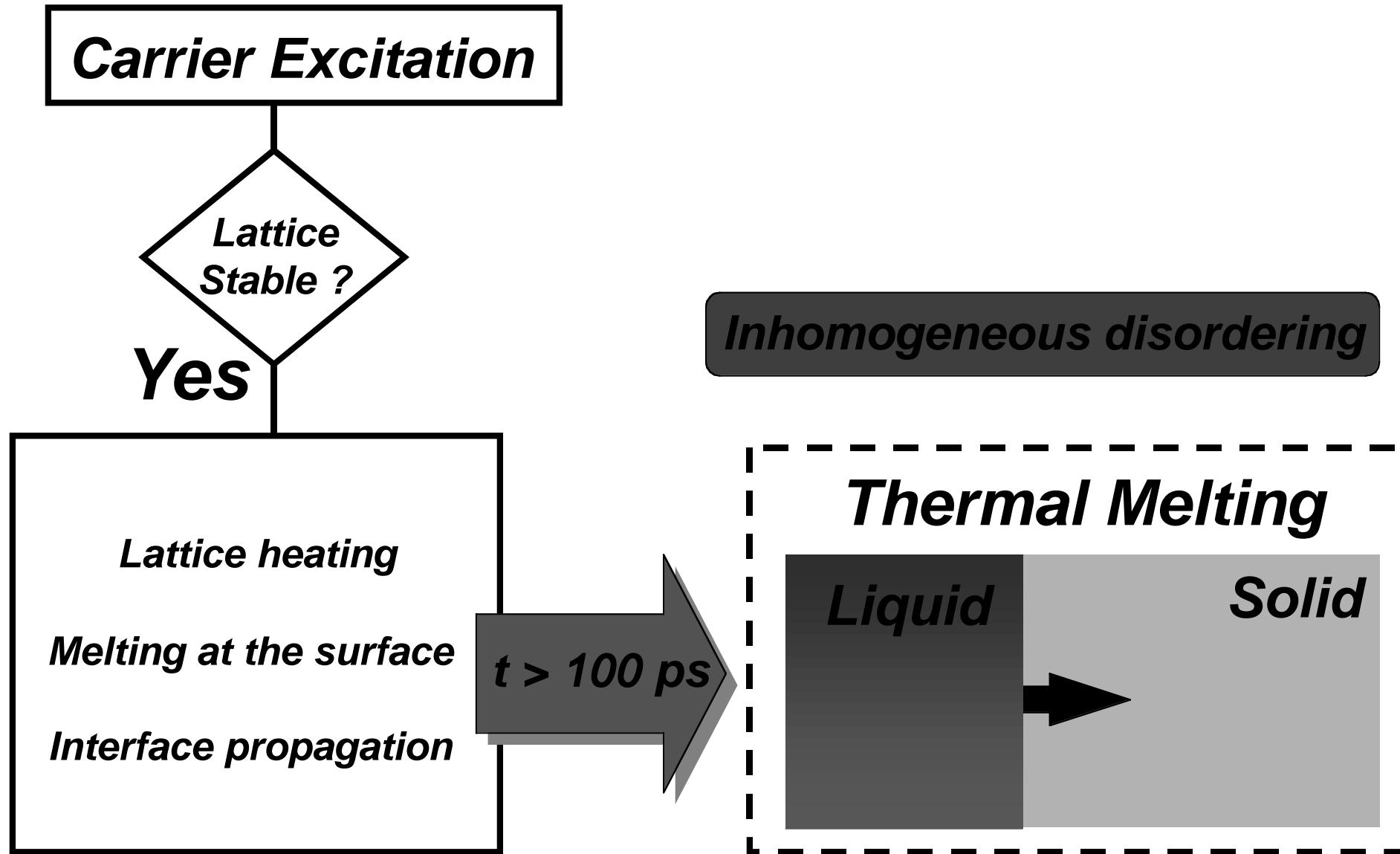


**$10^{22}$  excited carriers/cm<sup>3</sup>**

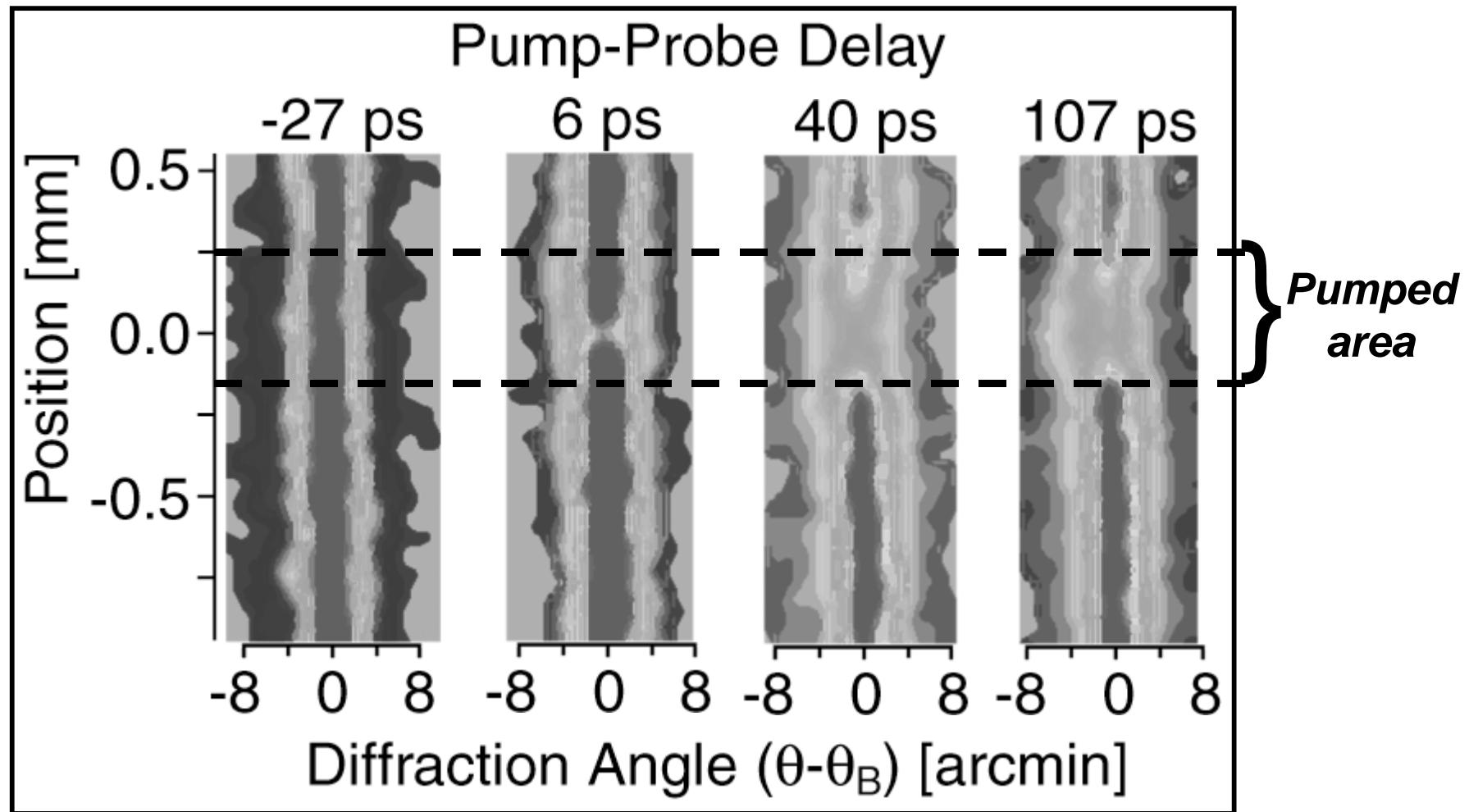
**25% valence electrons  
in the conduction band**

**Unstable lattice**

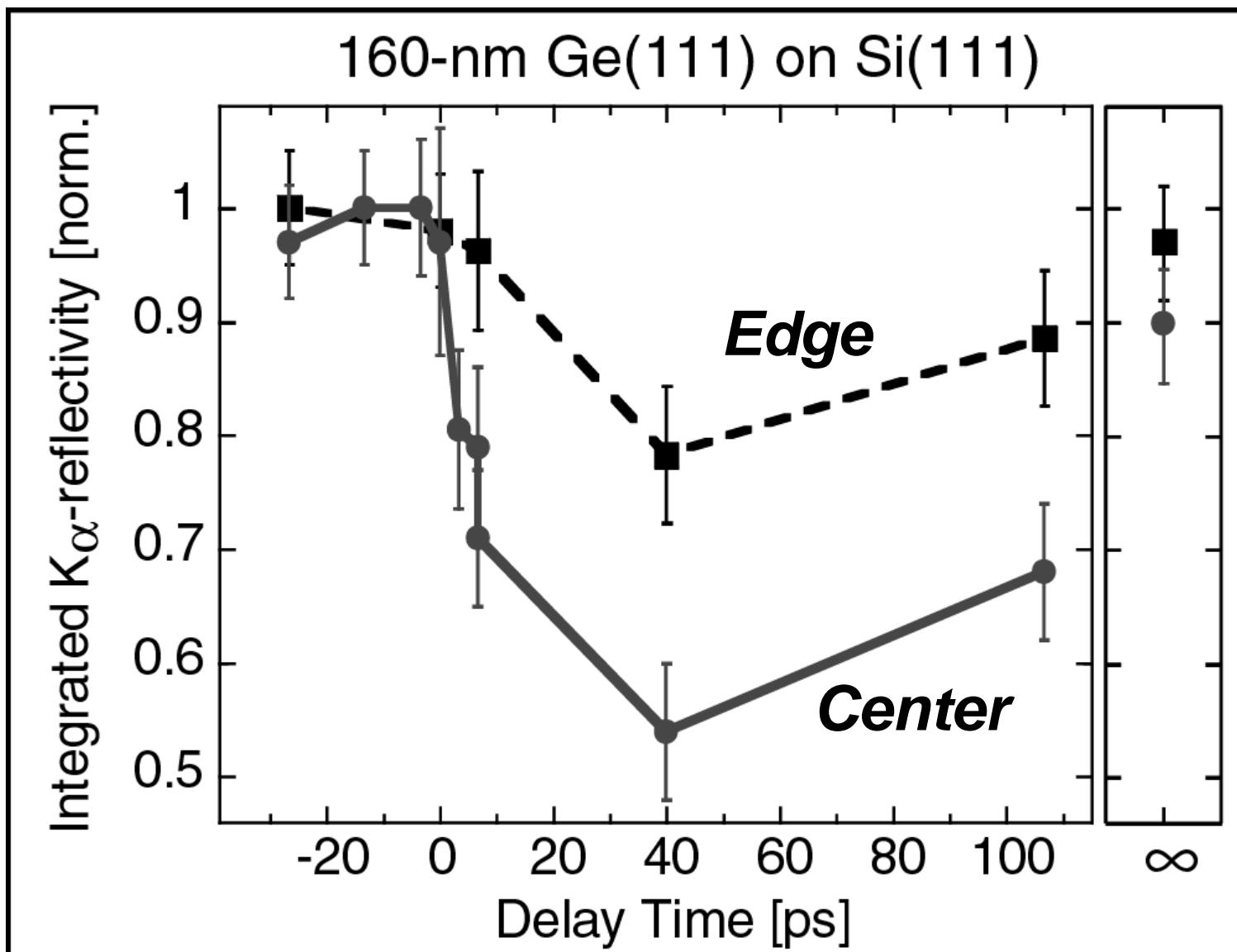
# *Ultrafast Melting Dynamics*



# *Ultrafast Melting in 160 nm Ge*



# *Ultrafast Melting: Integrated $K_{\alpha}$ Reflectivity*



# *Ultrafast Melting*



*160 nm*

**40 nm in < 7 ps**



**Homogeneous  
Disordering**



*Ge (111)*

*Si (111)*

# *Ultrafast Melting*

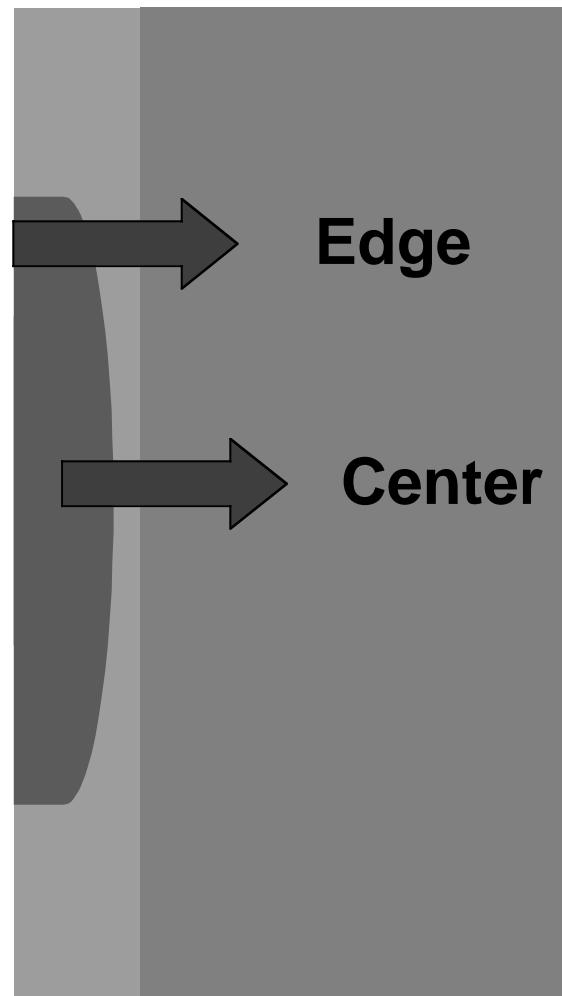


*160 nm*

**Inhomogeneous**

**Highly superheated solid**

**Interface velocity**  
 $V < 700 \text{ m / sec}$



*Ge (111)*

*Si (111)*

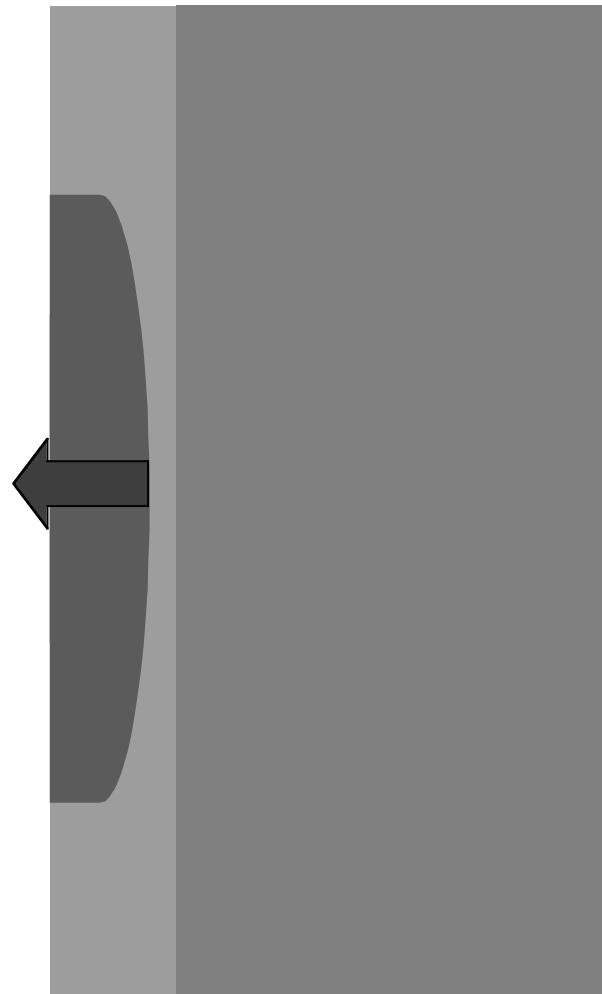
# *Ultrafast Melting*



*160 nm*

**Re-solidification**

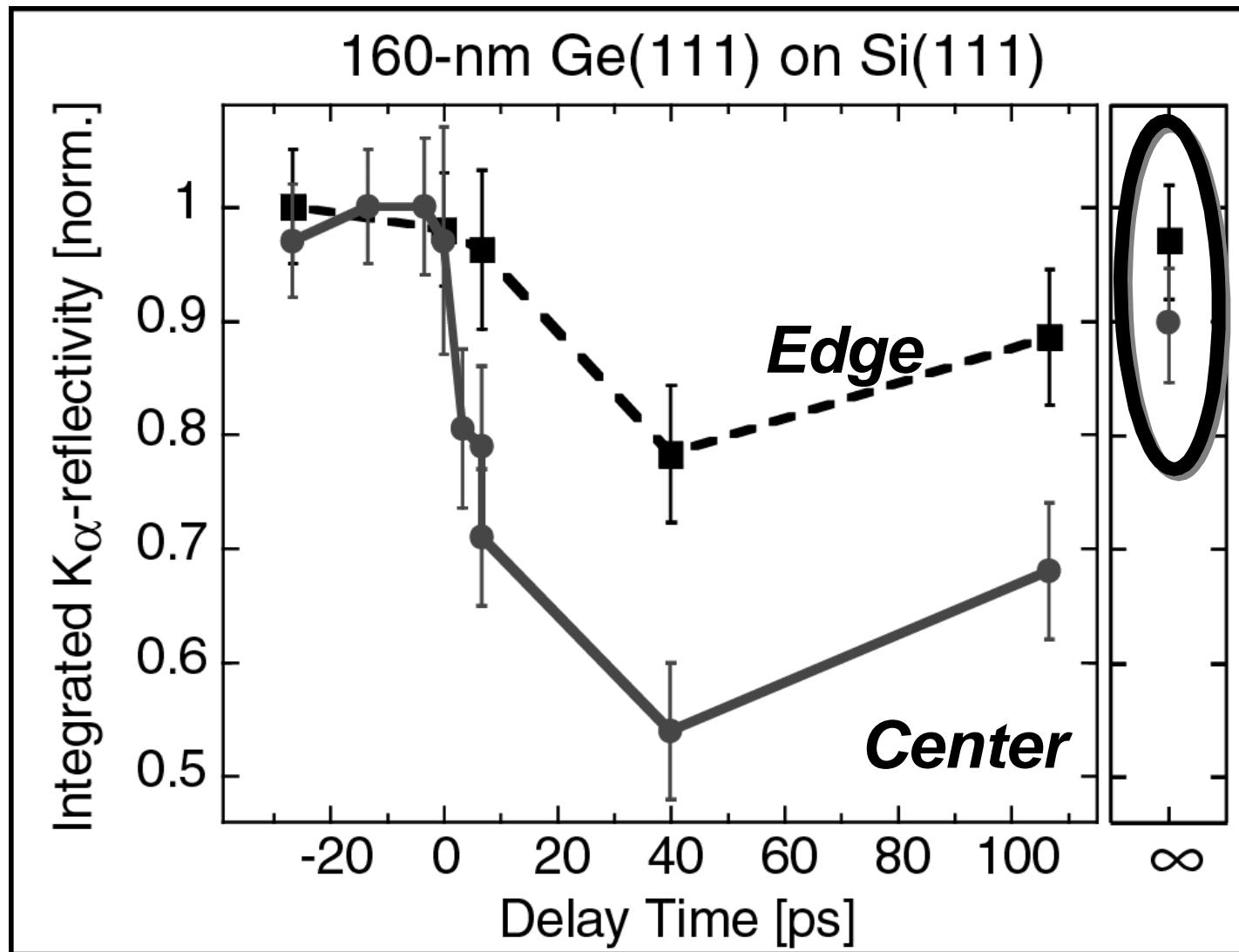
**Solid-liquid-solid**



*Ge (111)*

*Si (111)*

# *Ultrafast Melting: Integrated $K_{\alpha}$ Reflectivity*

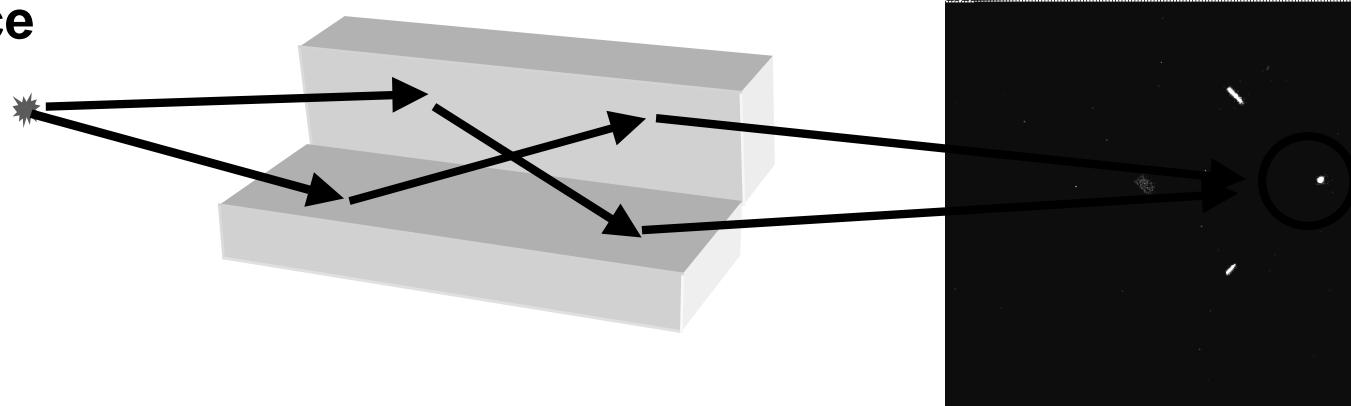


# X-ray Focusing



## Elliptical surfaces with graded Bragg coating

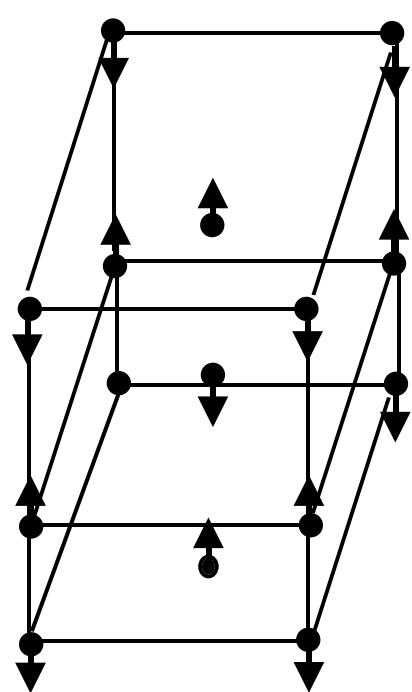
X-ray source



Spot diameter =  $54 \mu\text{m}$

2000 photons / shot

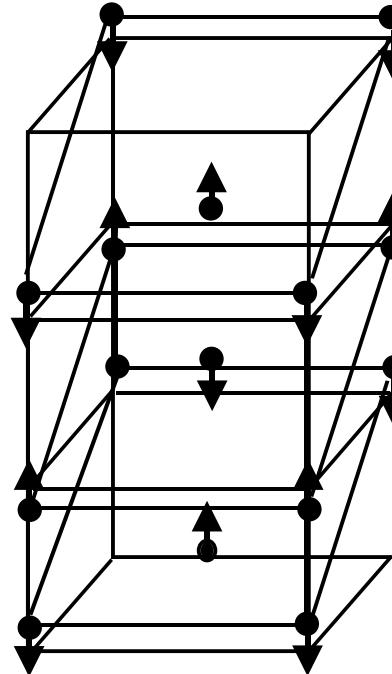
# *Structural Transition*



$T < 340 \text{ K}$

***Monoclinic***

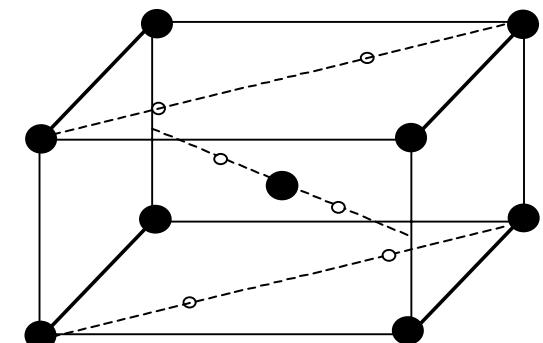
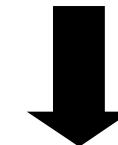
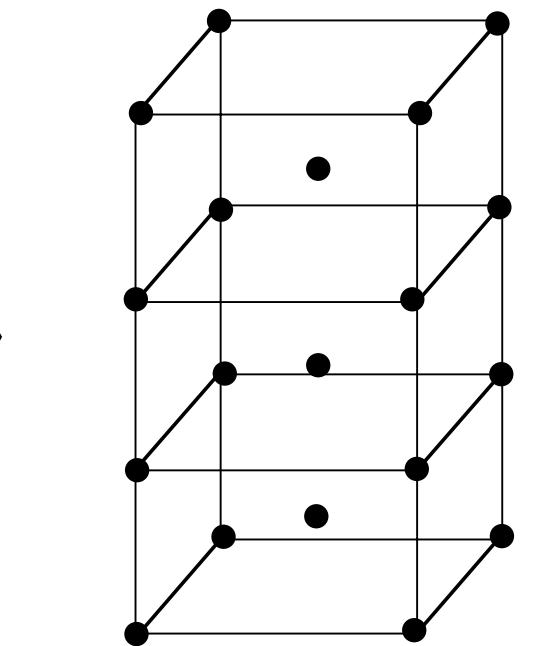
***Insulator***



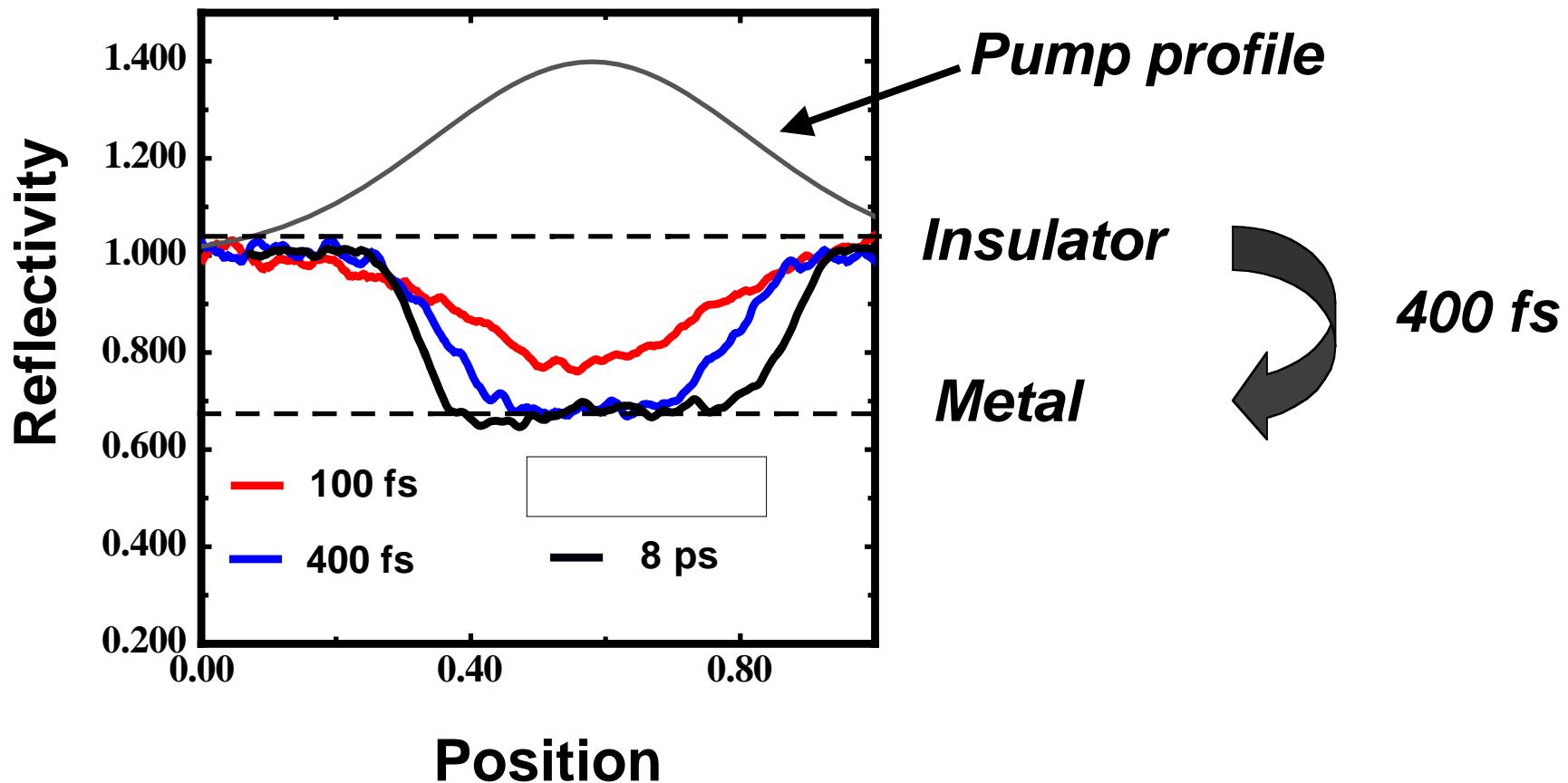
$T > 340 \text{ K}$

***Rutile***

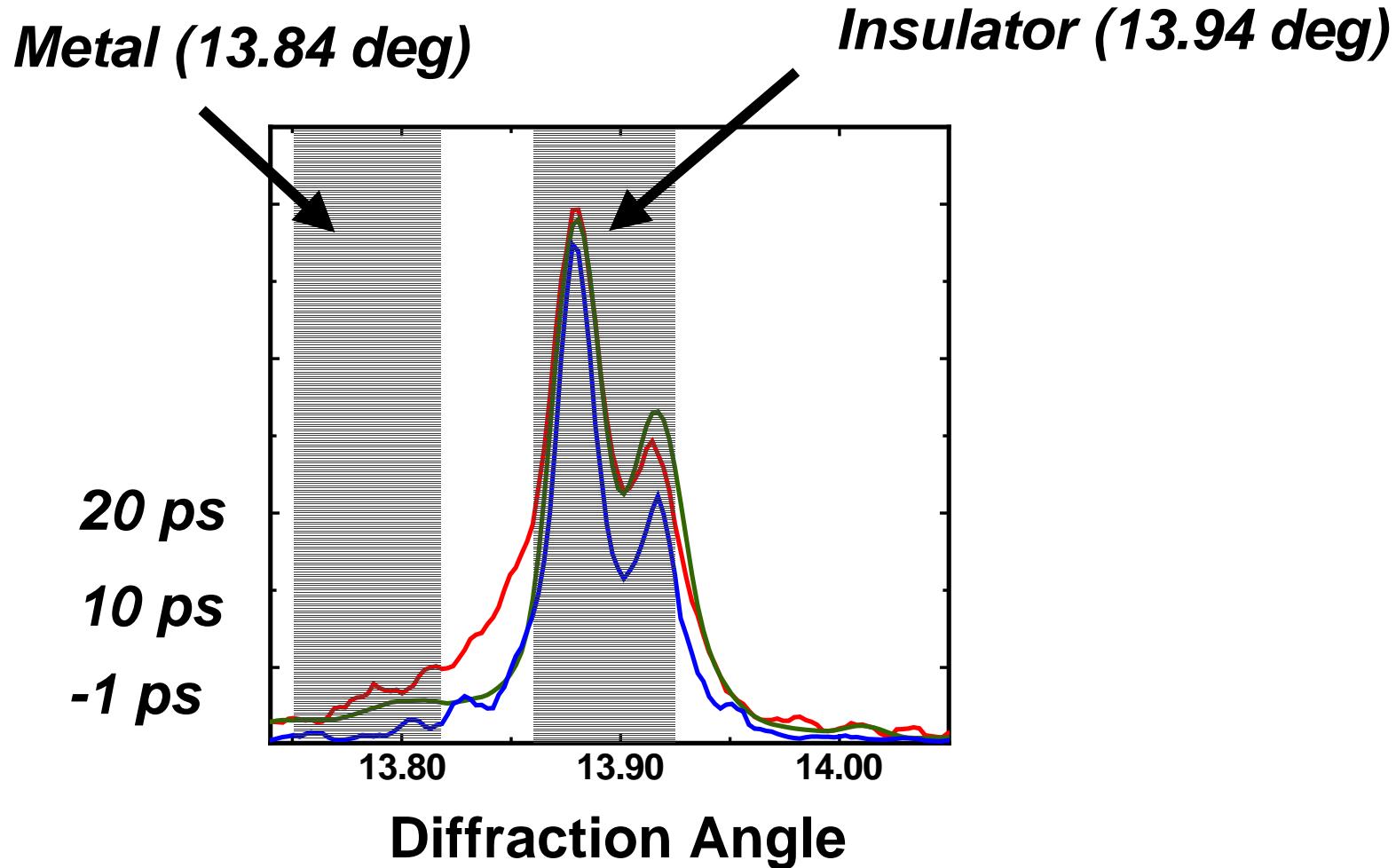
***Metallic***



# *Ultrafast Optical Data: Insulator to Metal*



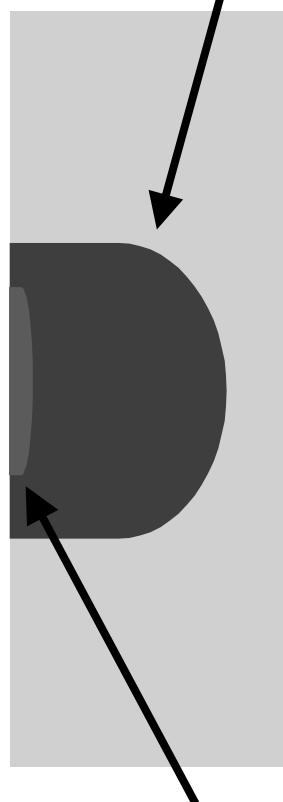
# *Ultrafast X-ray diffraction: bulk VO<sub>2</sub> (110)*



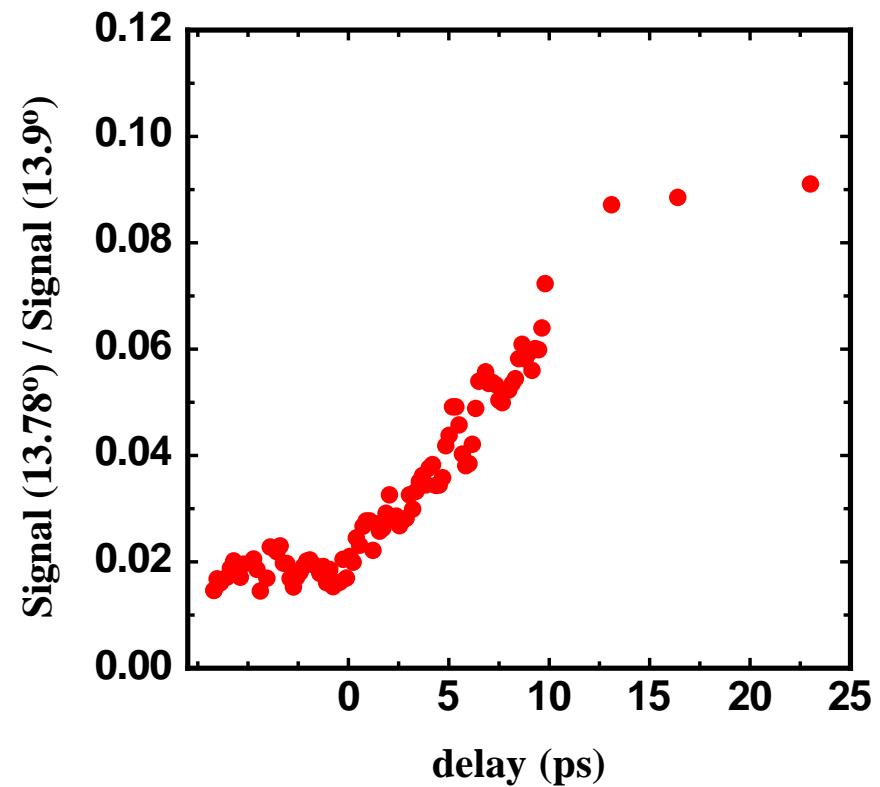
# *Time response*



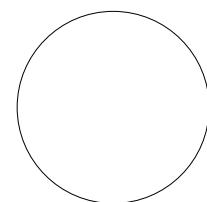
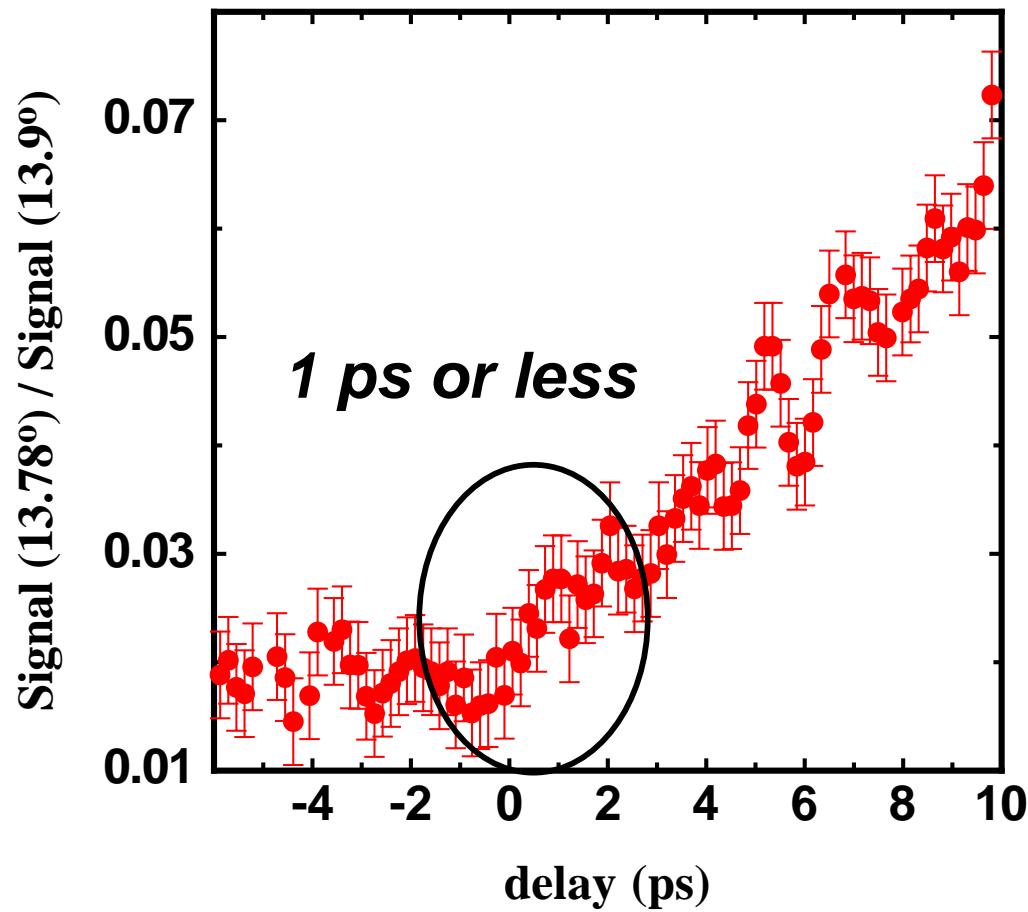
X-rays  $\approx$  3000 nm



Metallic phase  $\approx$  300 nm



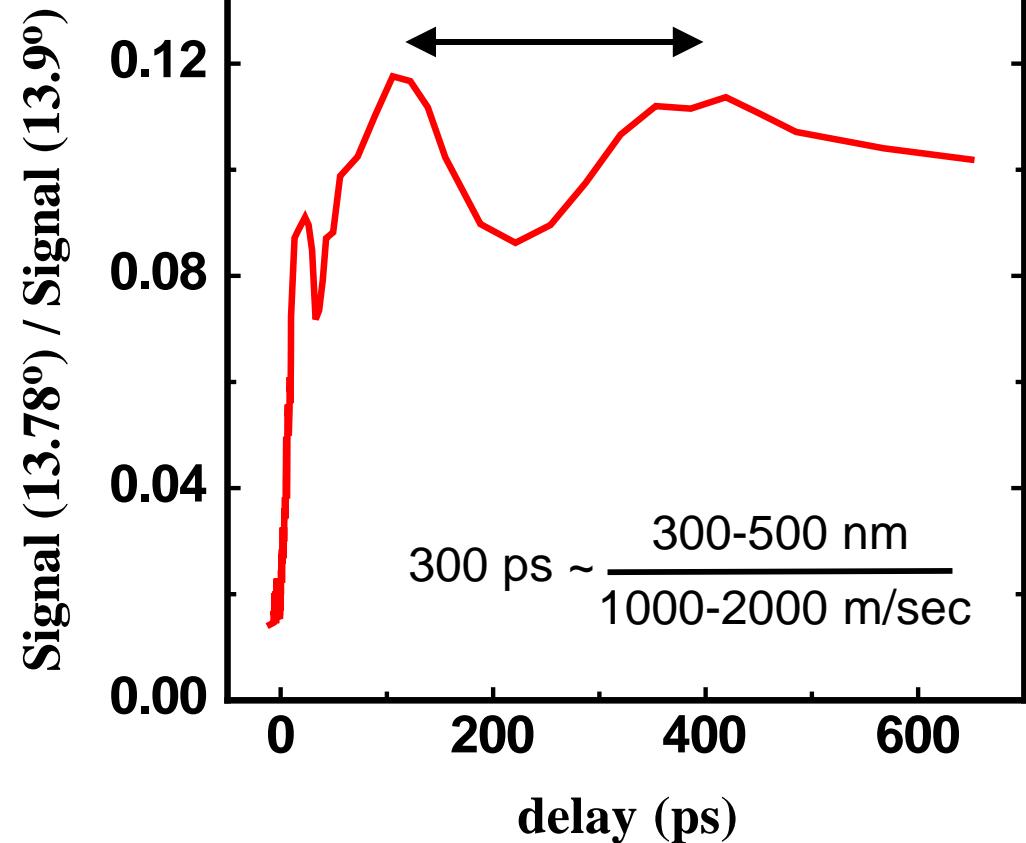
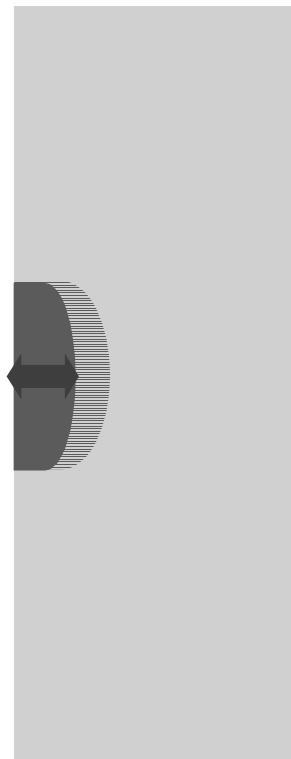
# *Time response*



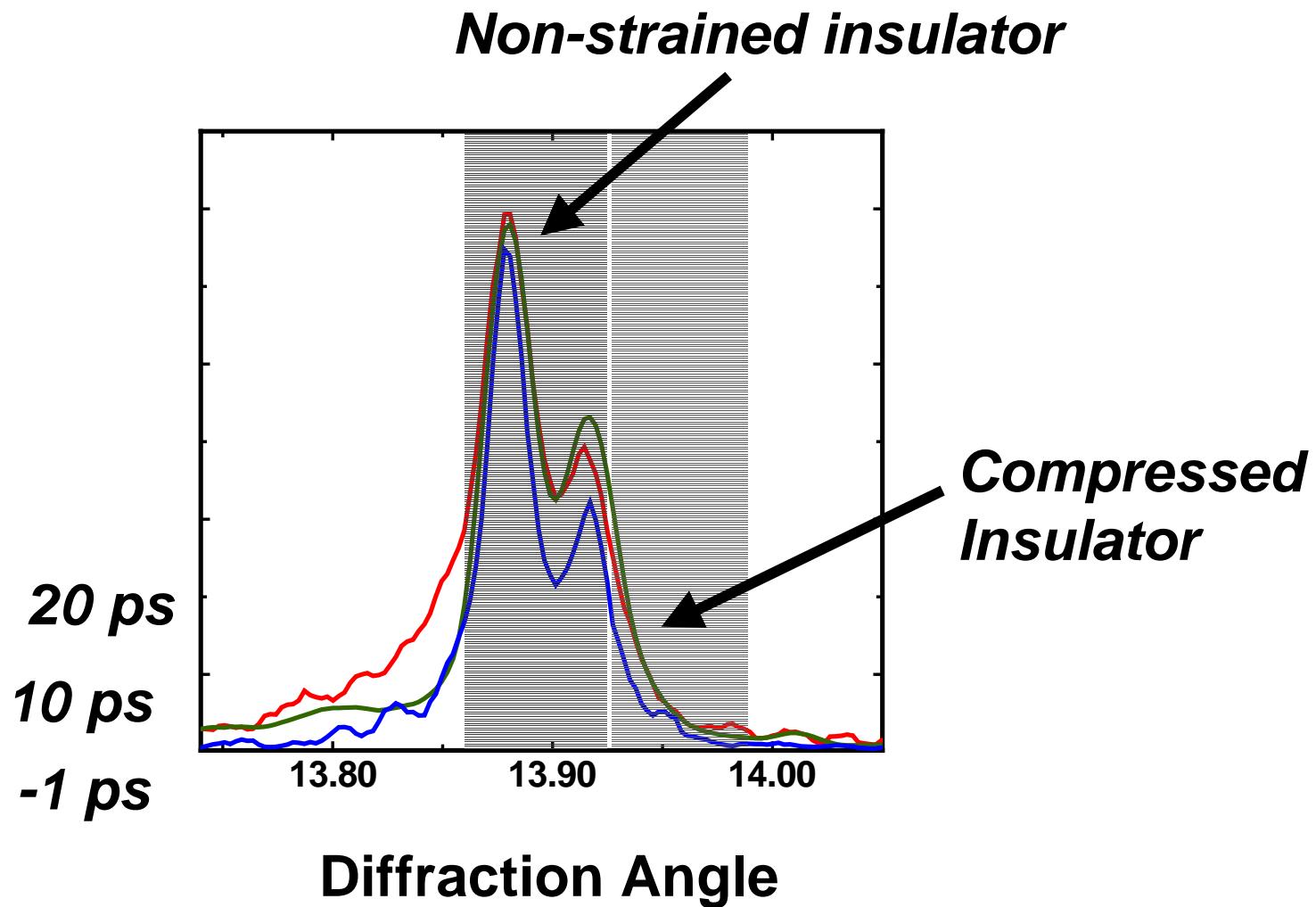
# *Long time response*



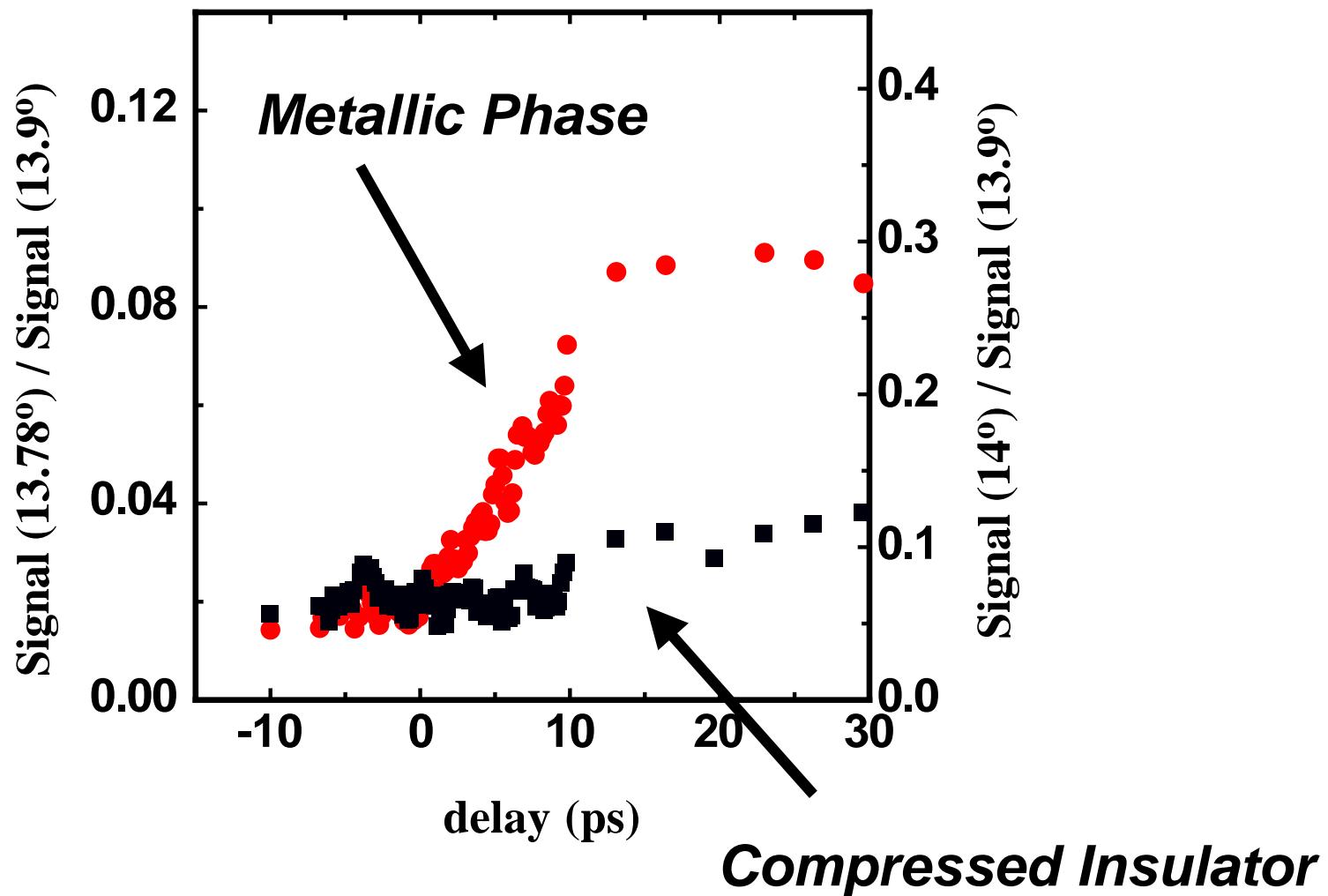
***Acoustic response ?***



# *Compression of the Insulating phase*



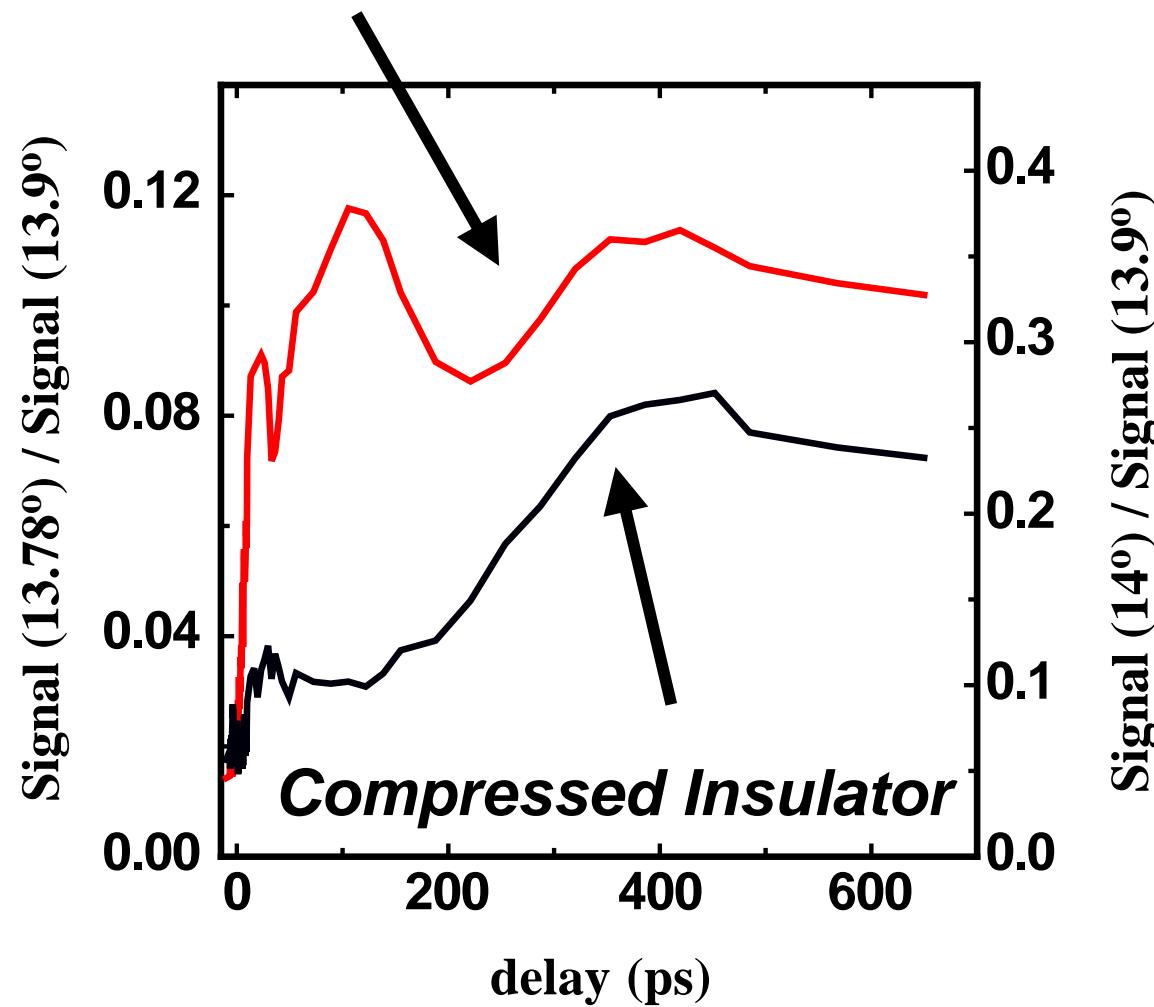
# *Compression of the insulating phase*



# *Compression of the insulating phase*

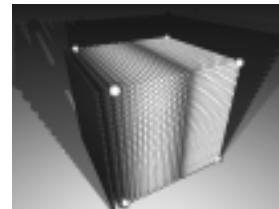


## **Metallic Phase**



# Summary and conclusion

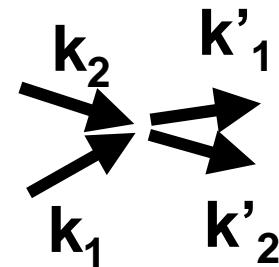
Coherent lattice transport



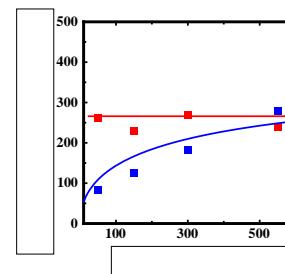
Lattice transport across buried interfaces



De-phasing of Acoustic phonons



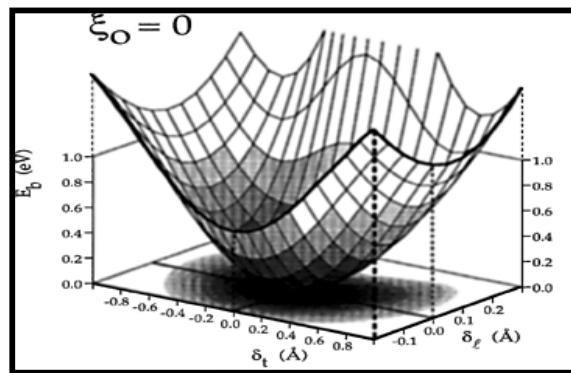
Heating depths and scaling laws for melting / ablation thresholds



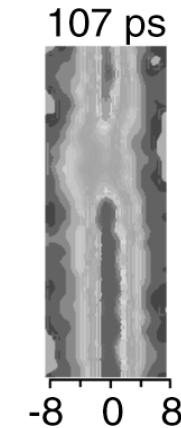
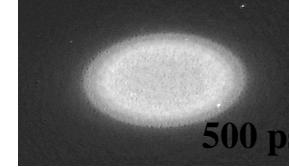
# Conclusion



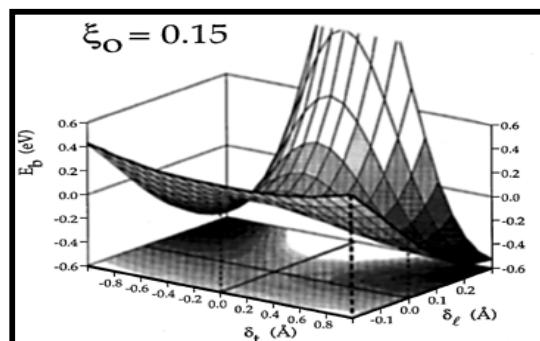
## Thermal melting



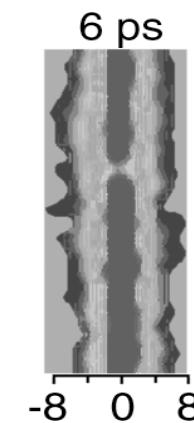
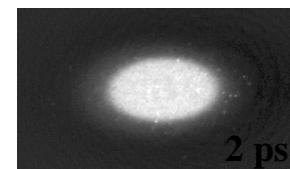
$t > 100 \text{ ps}$



## Non-thermal melting



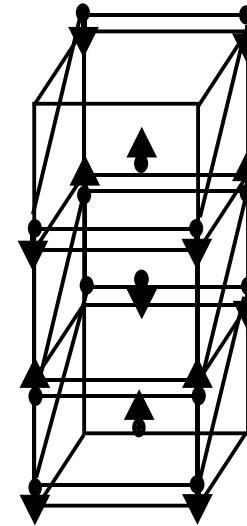
$t \approx 1 \text{ ps}$



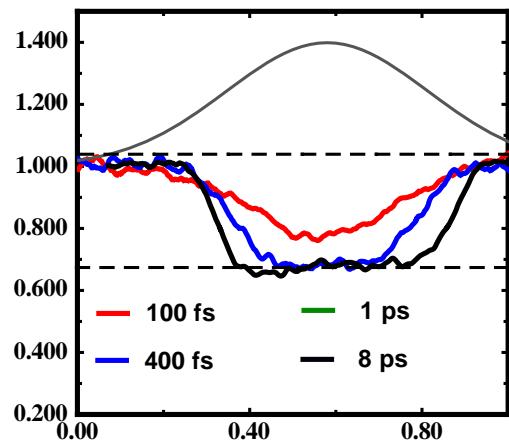
# Conclusions



## Solid-Solid phase transition in VO<sub>2</sub>



### Optical data



### X-ray data

